



US009087897B1

(12) **United States Patent**  
**Anderson et al.**

(10) **Patent No.:** **US 9,087,897 B1**  
(45) **Date of Patent:** **Jul. 21, 2015**

(54) **SEMICONDUCTOR STRUCTURES WITH PAIR(S) OF VERTICAL FIELD EFFECT TRANSISTORS, EACH PAIR HAVING A SHARED SOURCE/DRAIN REGION AND METHODS OF FORMING THE STRUCTURES**

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(\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/169,318**

(22) Filed: **Jan. 31, 2014**

(51) **Int. Cl.**  
**H01L 29/72** (2006.01)  
**H01L 29/78** (2006.01)  
**H01L 29/66** (2006.01)

(52) **U.S. Cl.**  
CPC ..... **H01L 29/7827** (2013.01); **H01L 29/66484** (2013.01); **H01L 29/66666** (2013.01); **H01L 29/7831** (2013.01)

(58) **Field of Classification Search**  
CPC ..... H01L 29/7813  
USPC ..... 257/329; 365/189.011  
See application file for complete search history.

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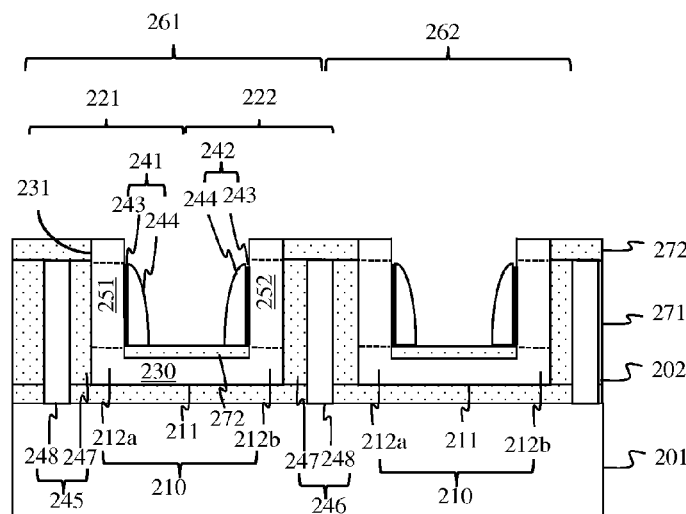
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(57) **ABSTRACT**

Disclosed are semiconductor structures and methods of forming the structures. The structures each comprise a pair of vertical FETs. Specifically, a U-shaped semiconductor body has a horizontal section and two vertical sections. The horizontal section comprises a shared source/drain region for first and second vertical FETs. Each vertical section comprises a channel region and a source/drain region above the channel region for a corresponding one of the vertical FETs. In one semiconductor structure, each vertical section has a gate wrapped around the channel region. In another semiconductor structure, each vertical section has a front gate positioned adjacent to the inner vertical surface at the channel region and a back gate positioned adjacent to the outer vertical surface at the channel region. In any case, a contact, which is electrically isolated from the gates, extends vertically to the shared source/drain region in the horizontal section. Optionally, metal strap(s) electrically connect the pair of vertical FETs to adjacent pair(s).

**20 Claims, 17 Drawing Sheets**



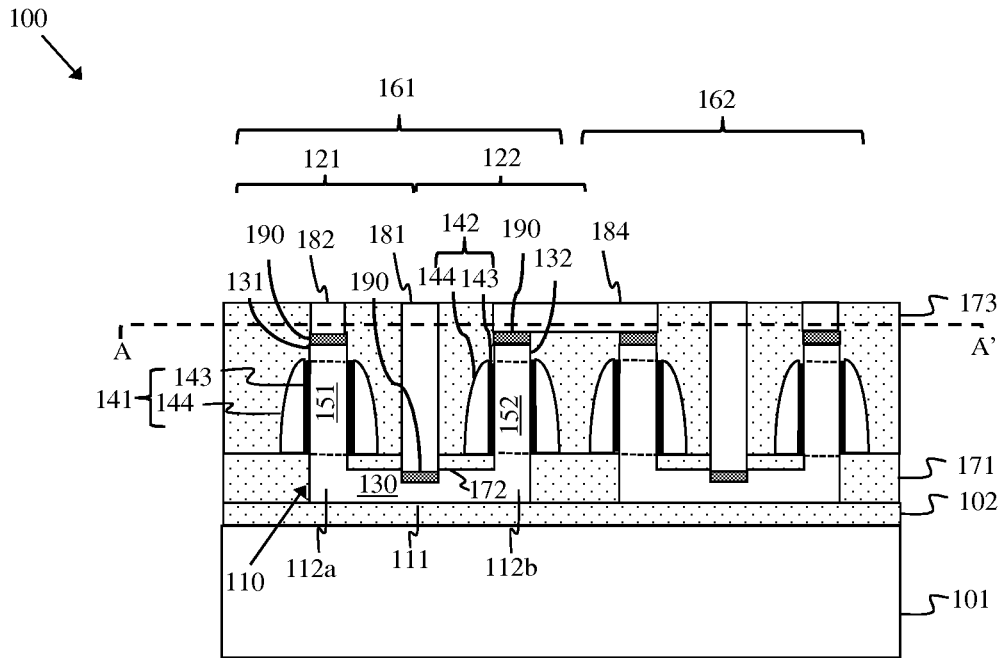


FIG. 1A

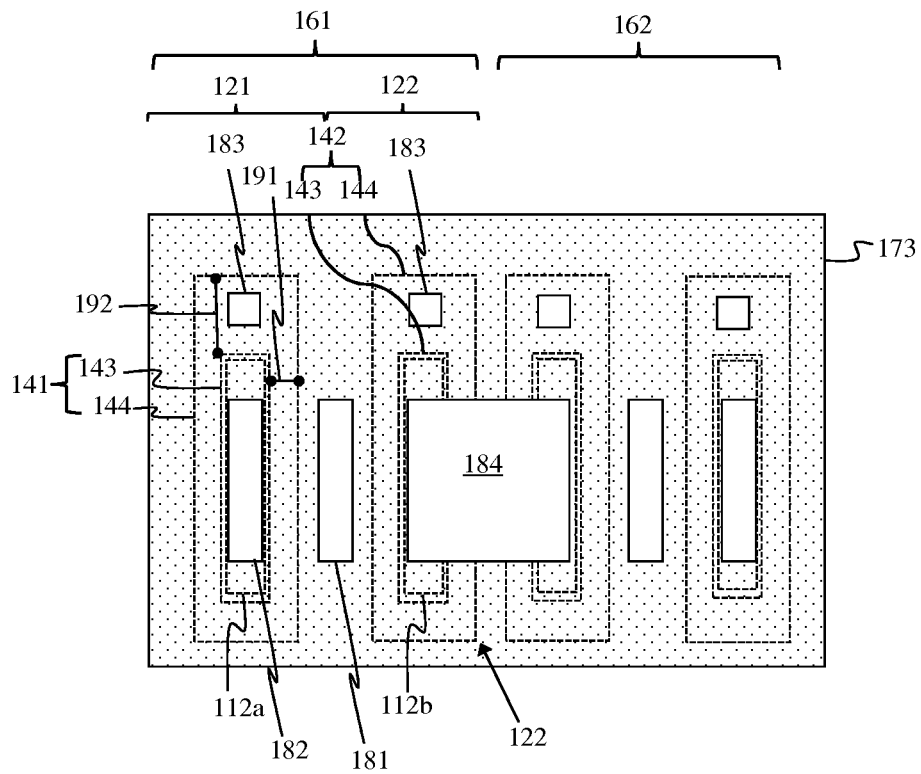


FIG. 1B

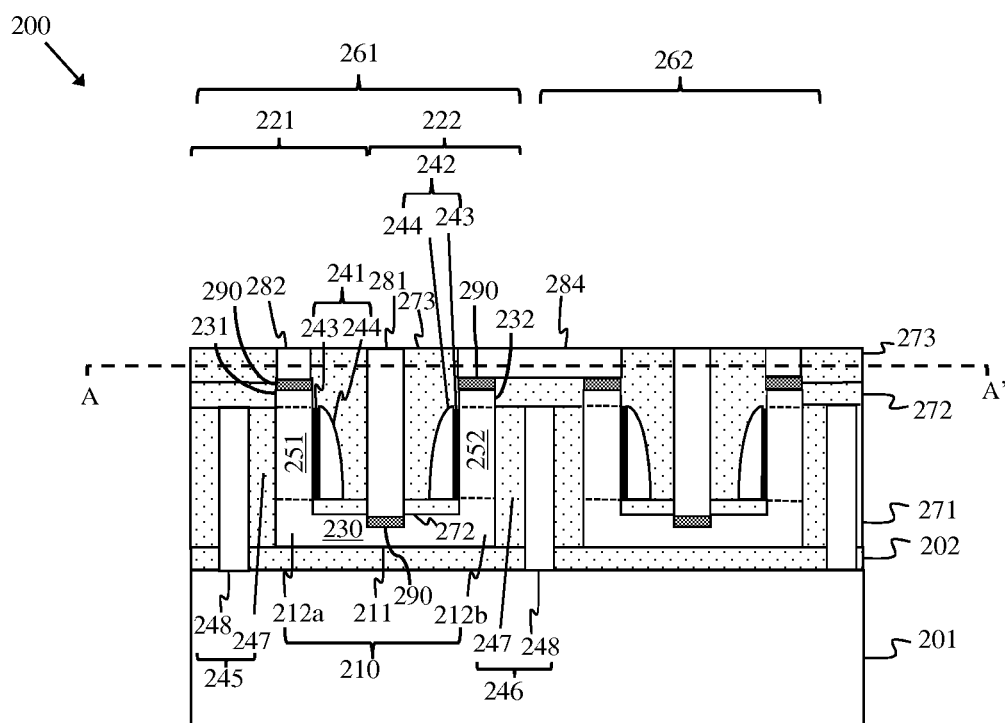


FIG. 2A

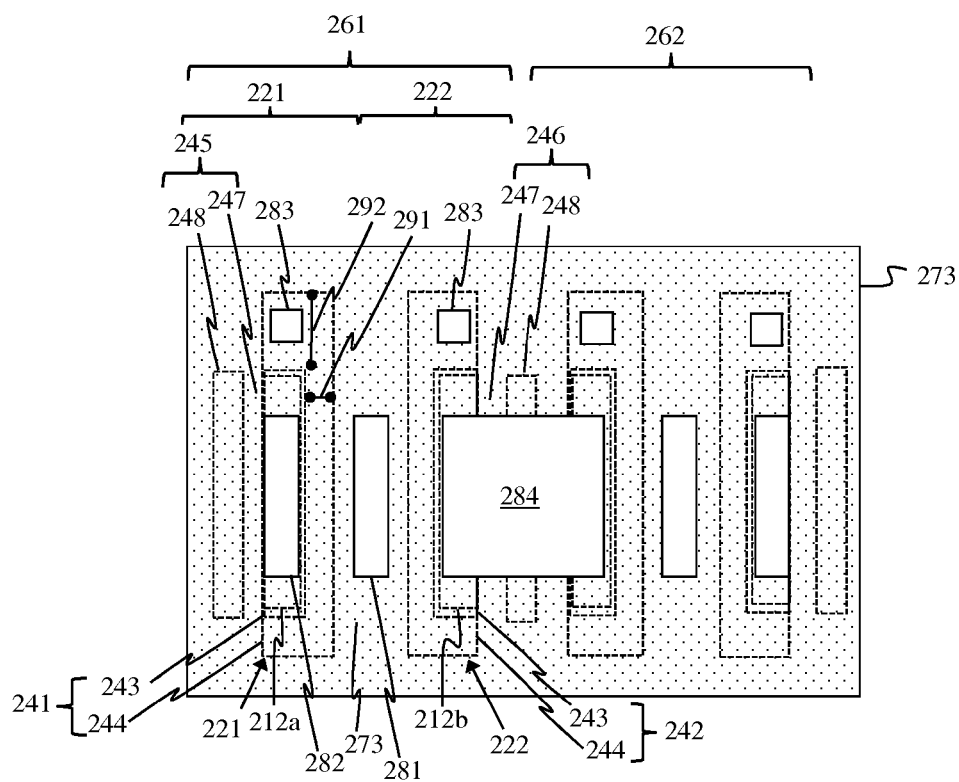


FIG. 2B

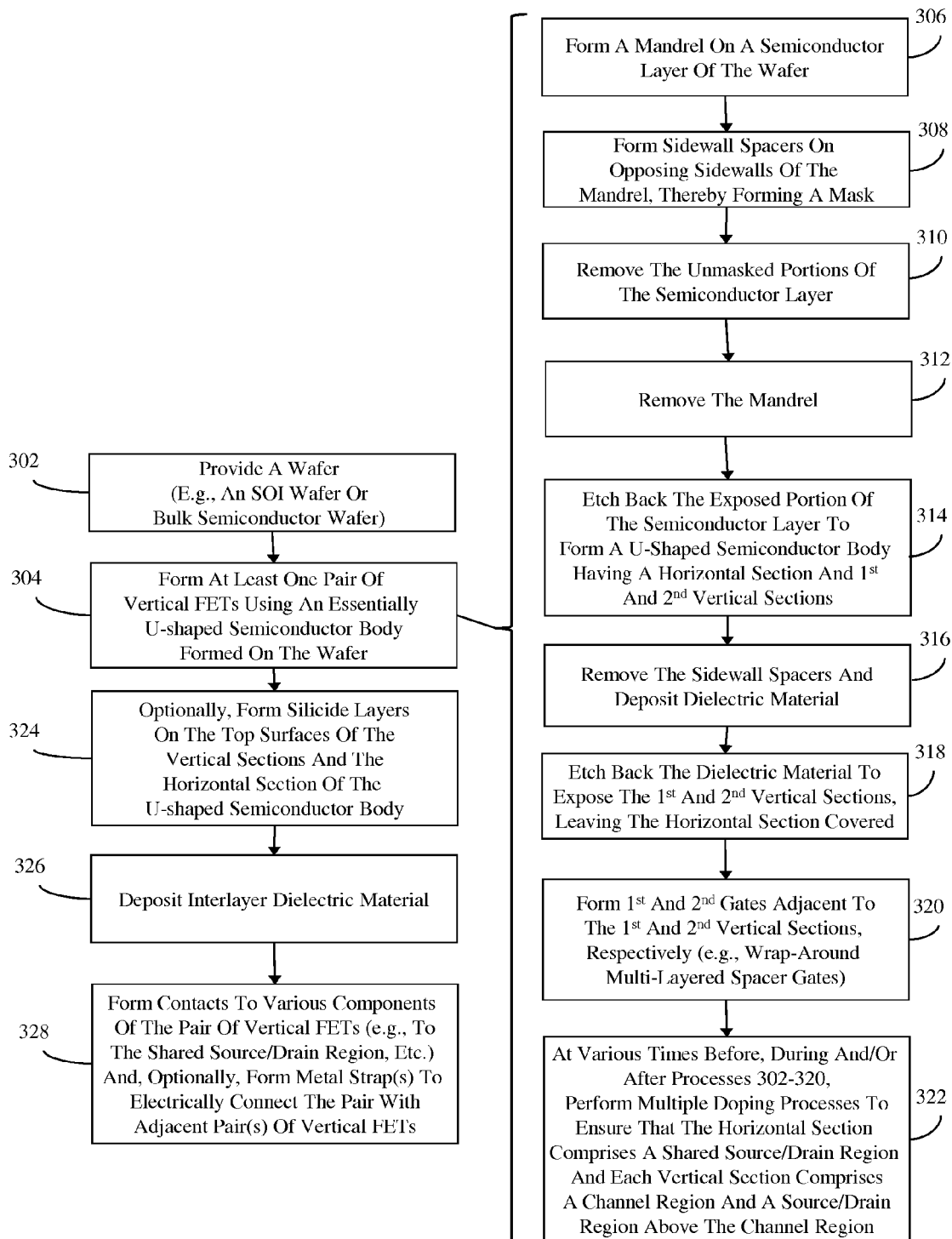


FIG. 3

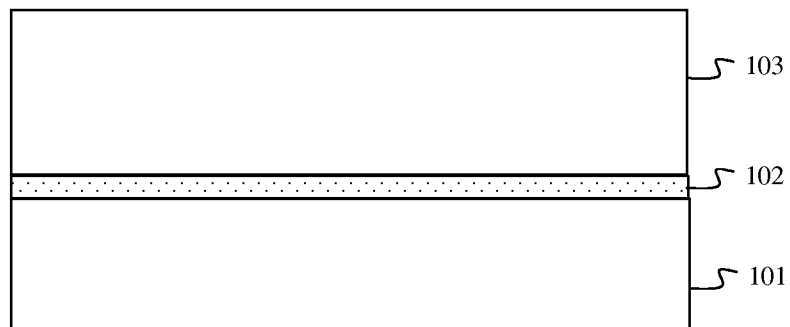


FIG. 4

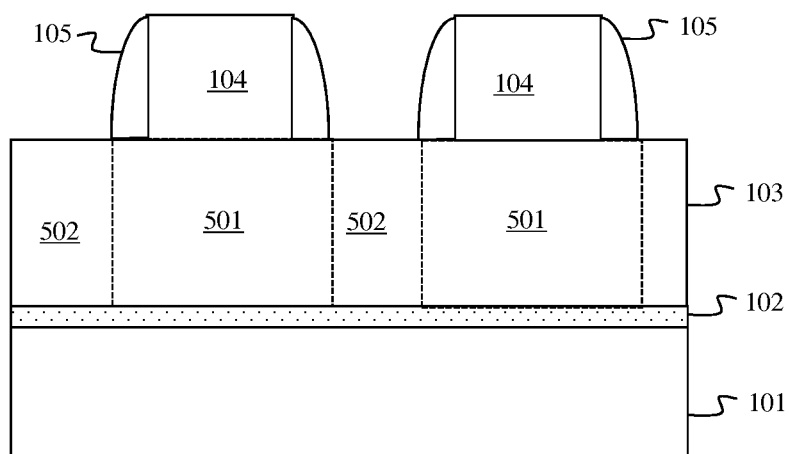


FIG. 5

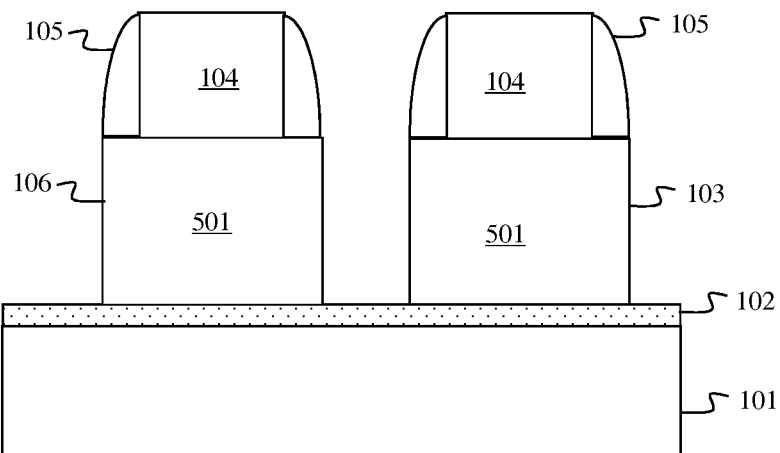


FIG. 6

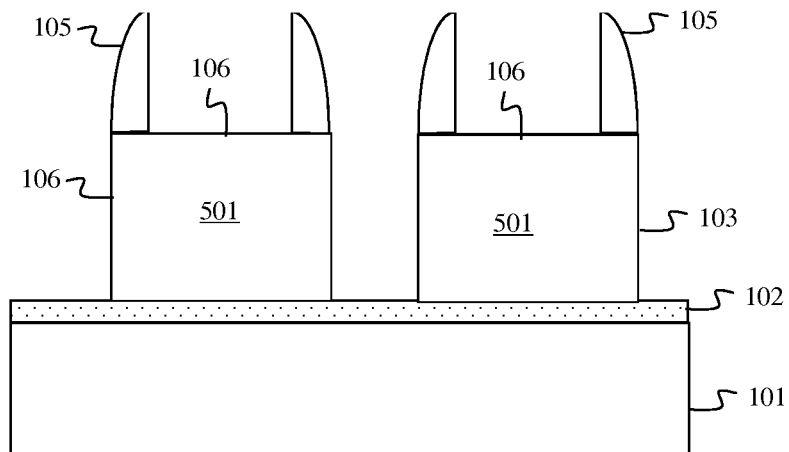


FIG. 7

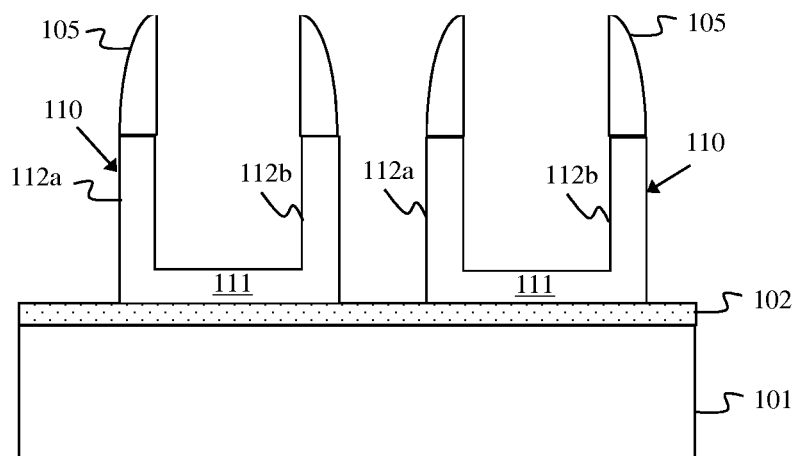


FIG. 8

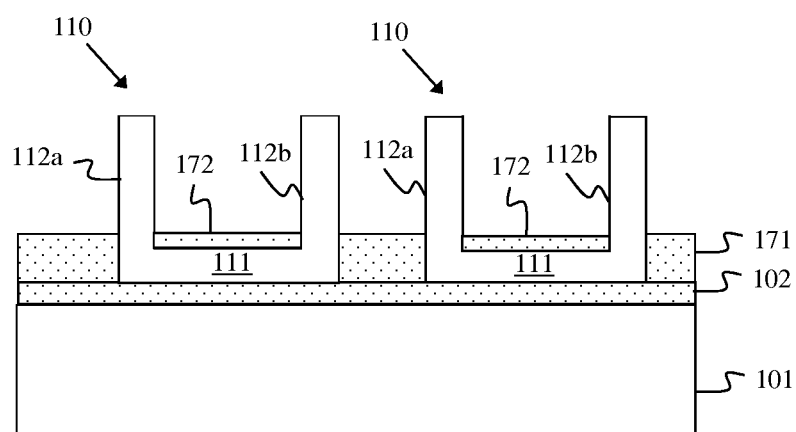


FIG. 9

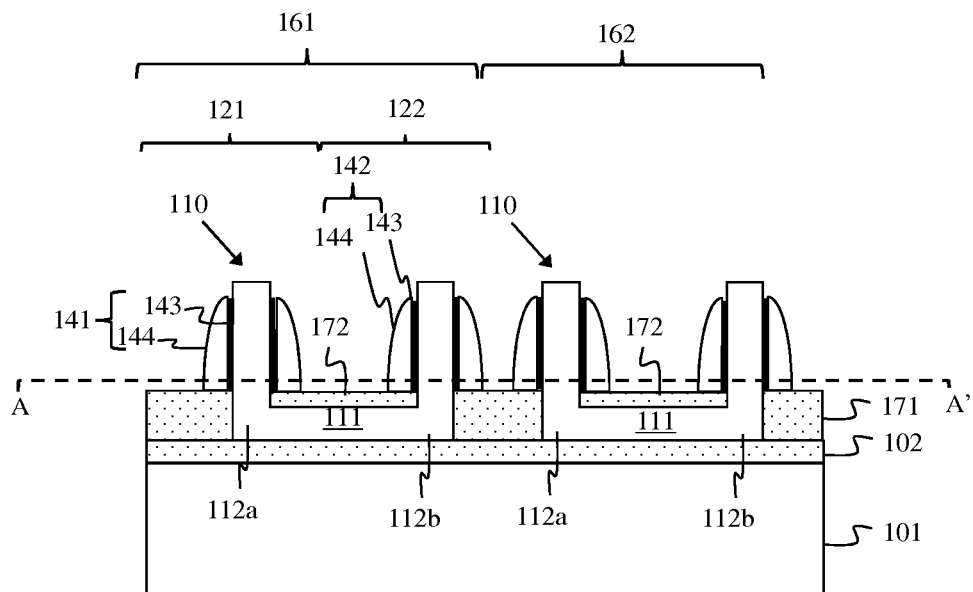


FIG. 10A

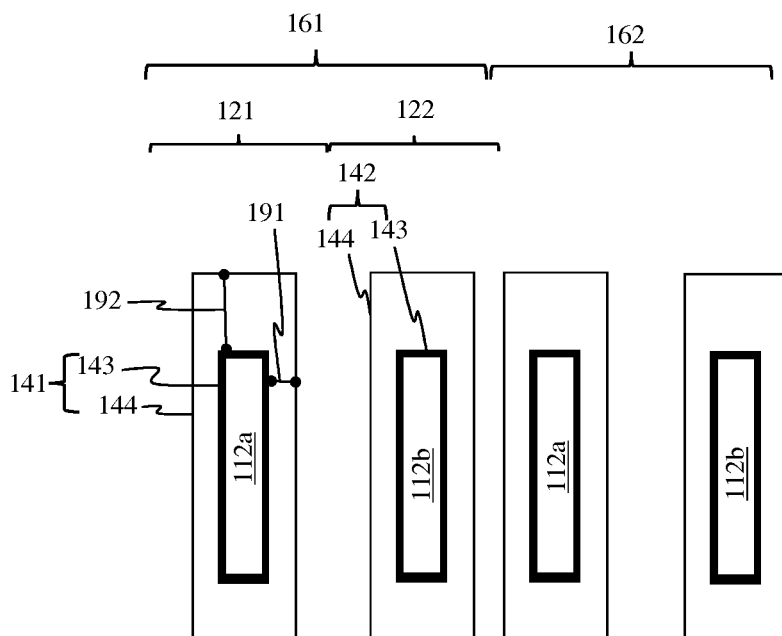


FIG. 10B



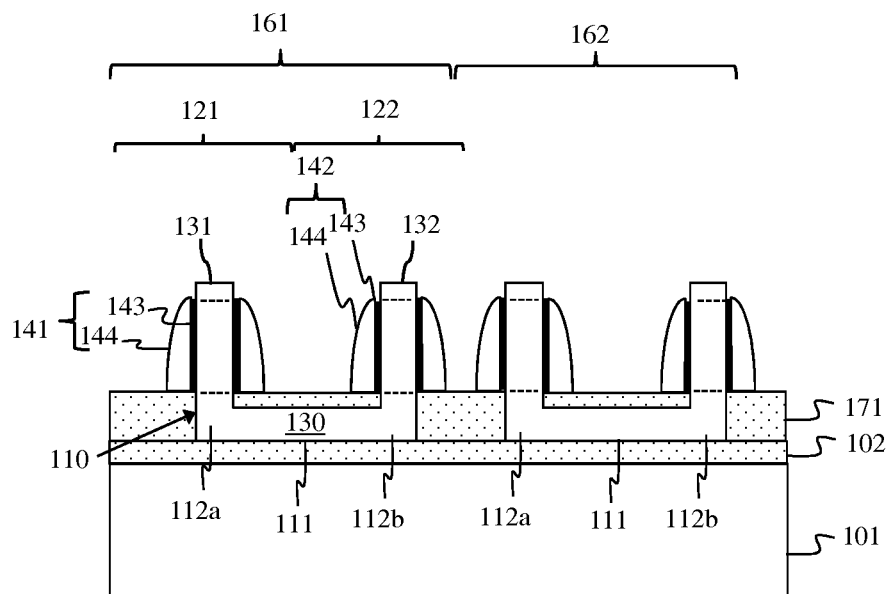


FIG. 11

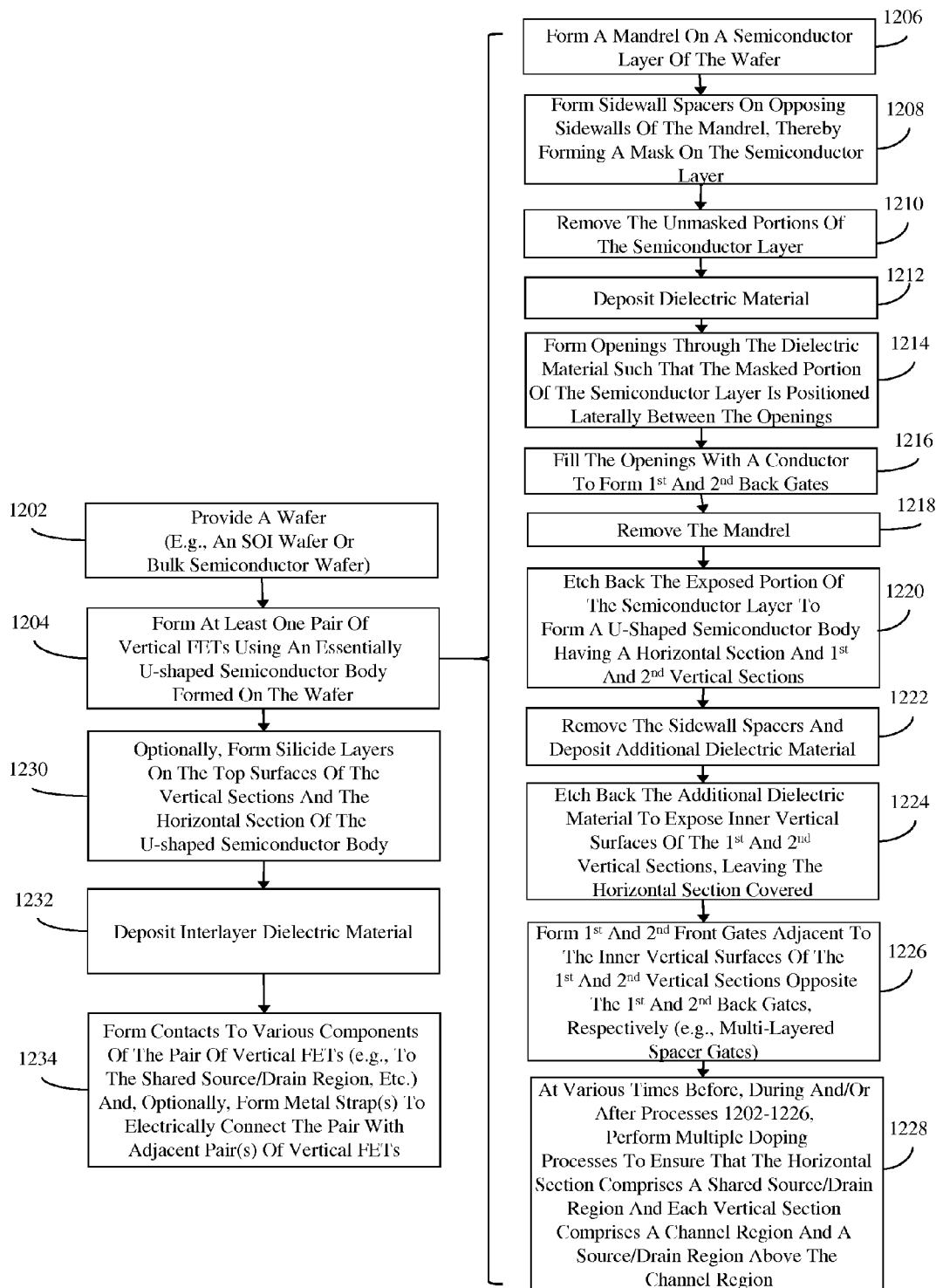


FIG. 12

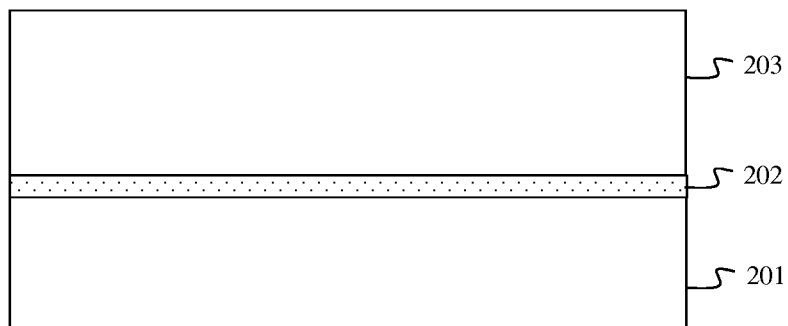


FIG. 13

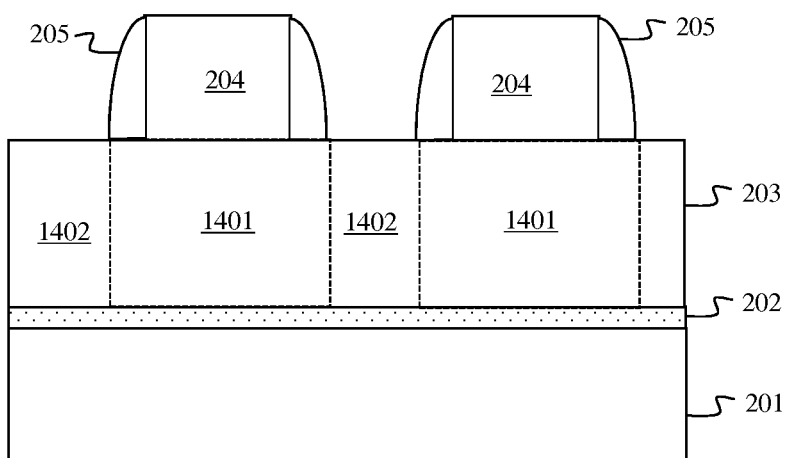


FIG. 14

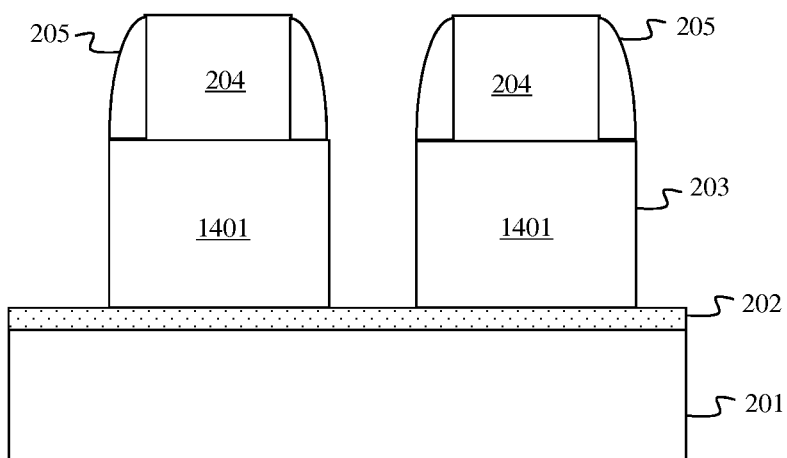


FIG. 15

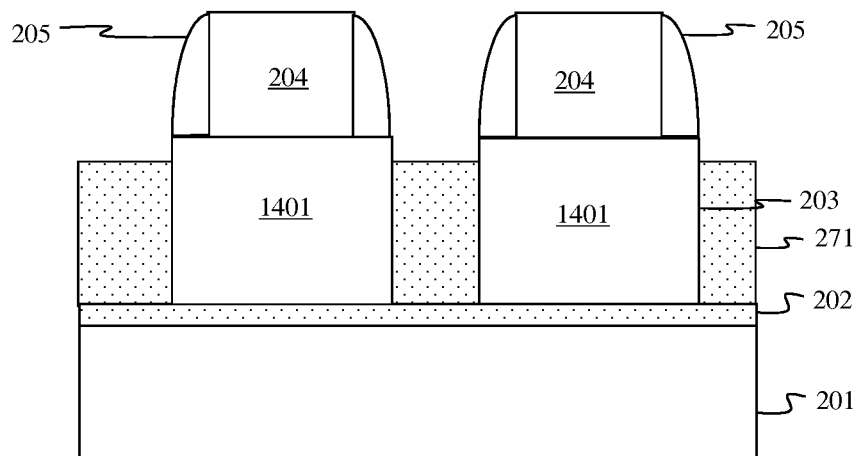


FIG. 16

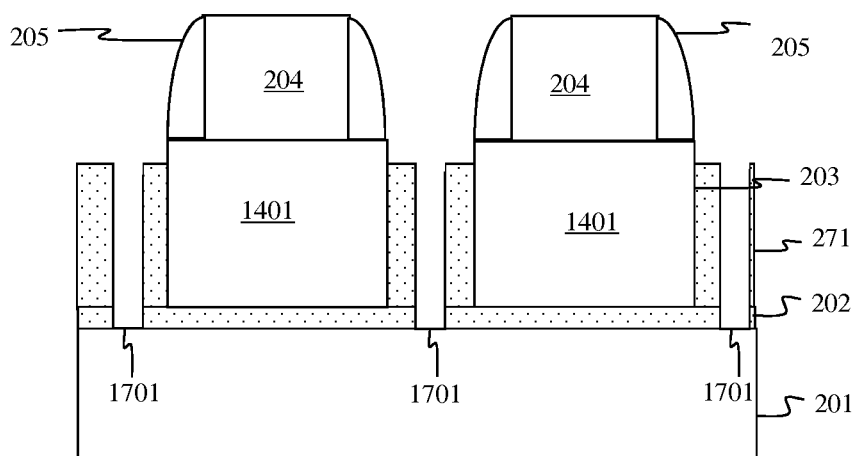


FIG. 17

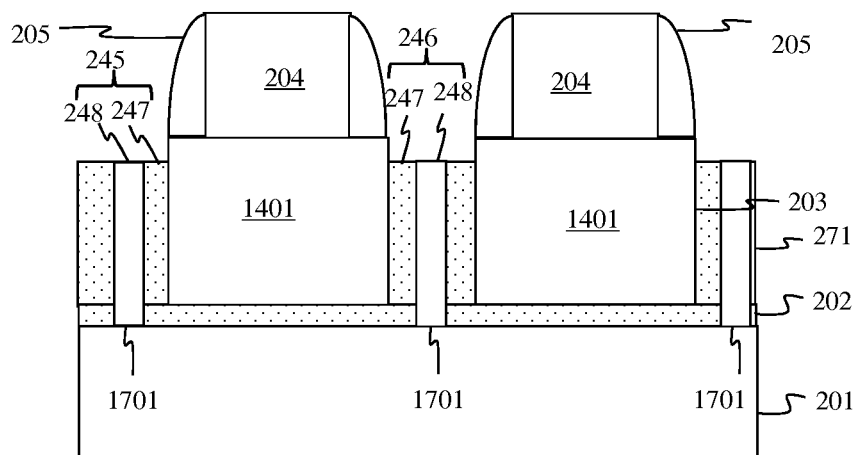


FIG. 18

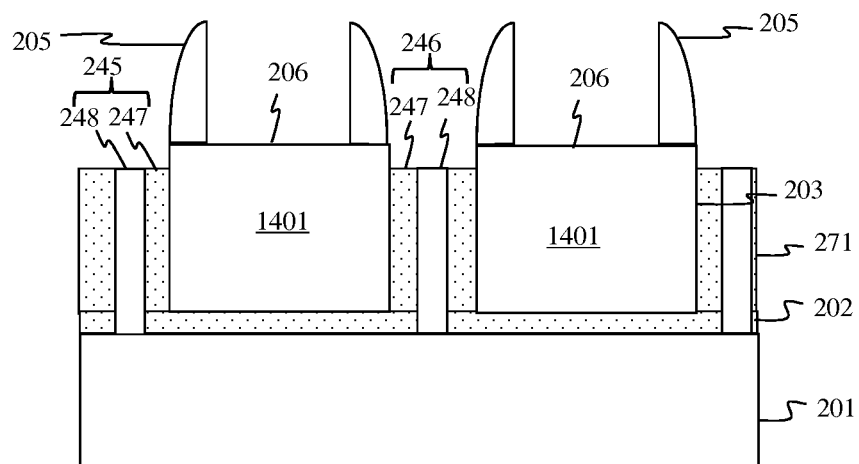


FIG. 19

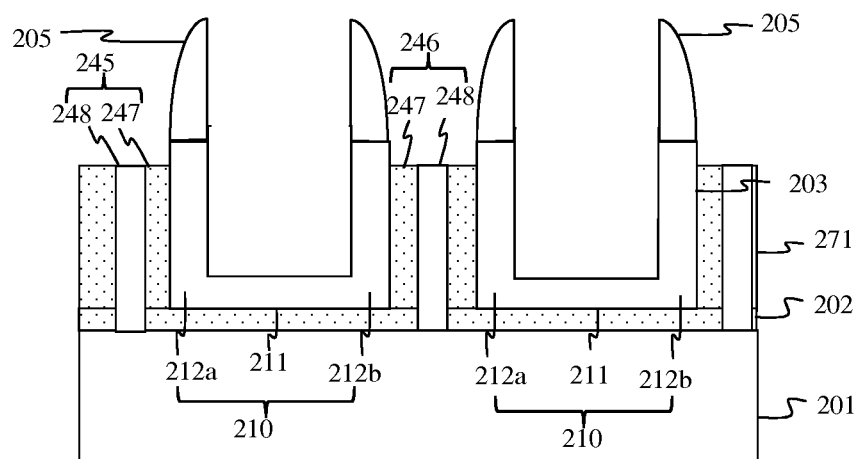


FIG. 20

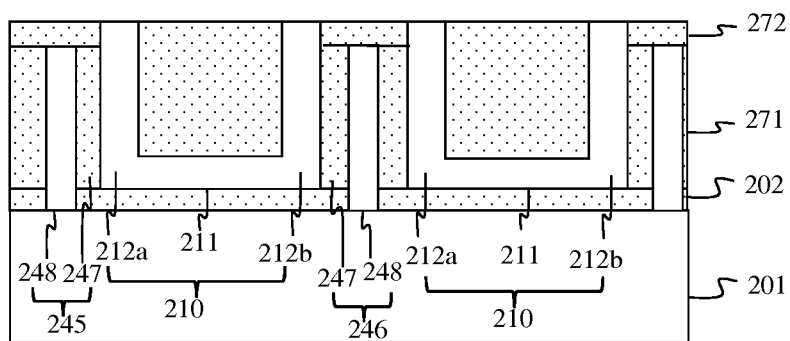


FIG. 21

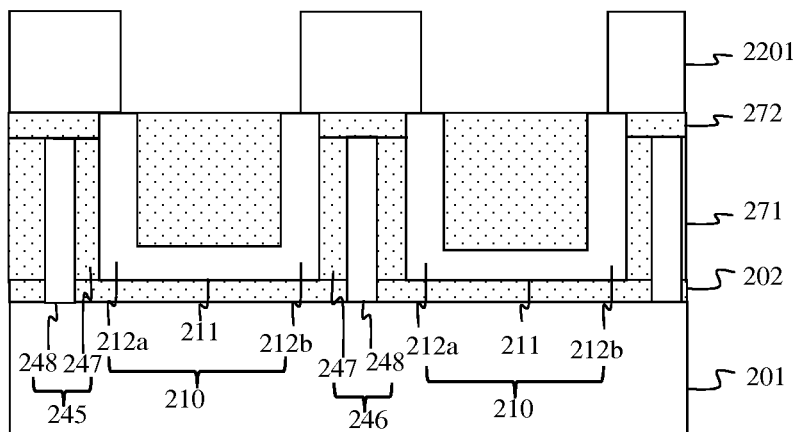


FIG. 22

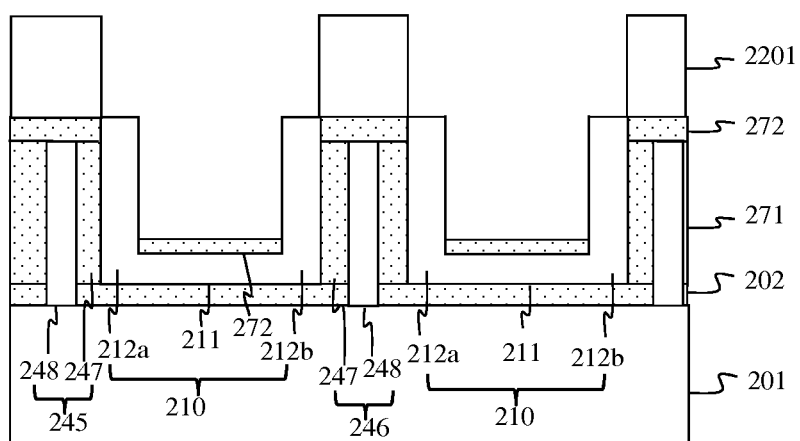


FIG. 23



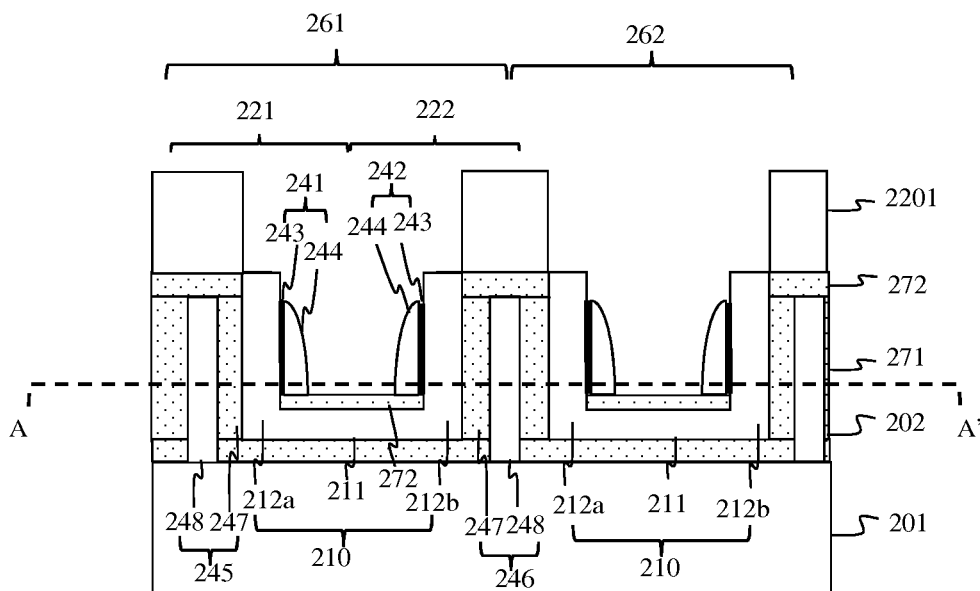


FIG. 24A

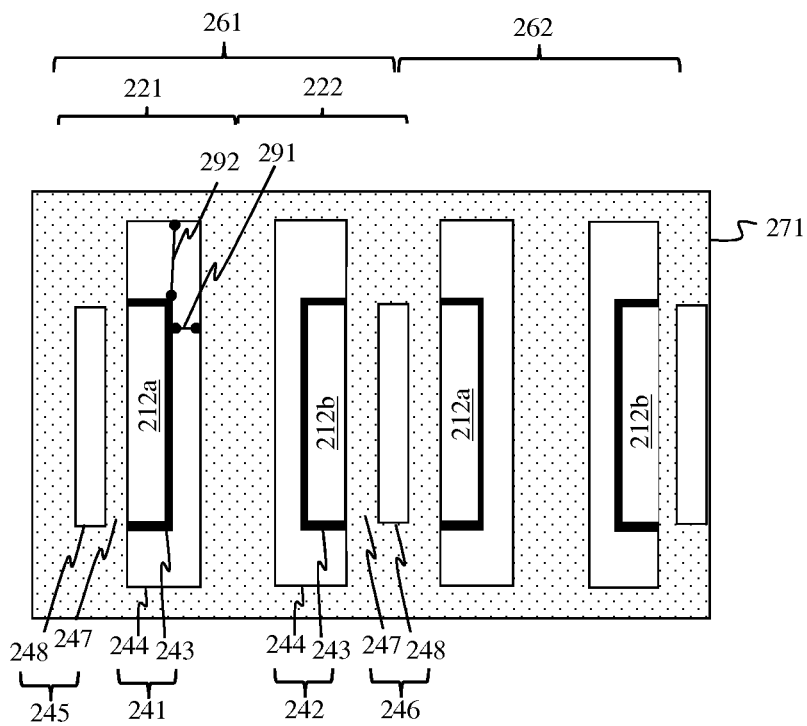


FIG. 24B

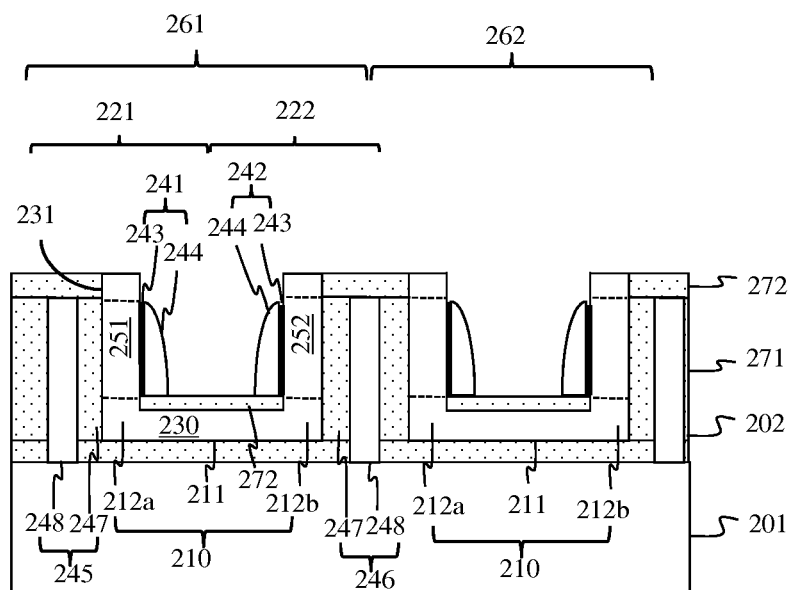


FIG. 25

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# SEMICONDUCTOR STRUCTURES WITH PAIR(S) OF VERTICAL FIELD EFFECT TRANSISTORS, EACH PAIR HAVING A SHARED SOURCE/DRAIN REGION AND METHODS OF FORMING THE STRUCTURES

## BACKGROUND

The present disclosure relates to semiconductor structures and methods and, more particularly, to semiconductor structures that comprise one or more pairs of vertical field effect transistors with each pair having a shared source/drain region and methods of forming such structures.

More particularly, integrated circuit design decisions are often driven by device scalability, manufacturing efficiency and costs. For example, size scaling of single-gate planar field effect transistors (FETs) resulted in devices with a smaller channel length. Unfortunately, the smaller channel length resulted in a corresponding increase in short channel effects and a decrease in drive current. In response, different types of multi-gate non-planar field effect transistors (MUGFETs), such as dual-gate non-planar FETs (also referred to herein as fin-type FETs (FINFETs)) and tri-gate non-planar FETs, which comprise one or more semiconductor fins, were developed in order to provide reduced-size field effect transistors, while simultaneously avoiding corresponding increases in short channel effects and decreases in drive current. Unfortunately, further size scaling of conventional MUGFETs has been limited by the required specifications for the different features of such devices. For example, a minimum gate length is required in order to switch a MUGFET on and off. This minimum gate length must, in turn, be considered in setting the pitch between source/drain contacts. Additionally, in MUGFETs that incorporate multiple semiconductor fins to increase transistor width and, thereby drive current, the pitch between semiconductor fins must be sufficiently large so as to allow for deposition of gate material between the semiconductor fins. Finally, the thickness of the semiconductor layer used to form the MUGFET must be equal to the height of the semiconductor fin(s). Therefore, there is a need in the art for a semiconductor structure and method of forming the structure that allows for further size scaling of FETs over what has heretofore been available with conventional planar FETs and MUGFETs.

## SUMMARY

In view of the foregoing, disclosed herein are semiconductor structures configured to allow for continued size scaling of field effect transistors. The semiconductor structures each comprise a pair of vertical field effect transistors formed from an essentially U-shaped semiconductor body. This semiconductor body has a horizontal section and first and second vertical sections. The horizontal section can comprise a shared source/drain region for first and second vertical field effect transistors. The first and second vertical sections can each comprise a channel region and a source/drain region above the channel region for the first and second vertical field effect transistors, respectively. In one semiconductor structure, each vertical section has a gate wrapped around the channel region. In another semiconductor structure, each vertical section has a front gate positioned adjacent to the inner vertical surface at the channel region and a back gate positioned adjacent to the outer vertical surface at the channel region. In any case, a contact, which is electrically isolated from the gates, can extend vertically to the shared source/drain region in the horizontal section. Optionally, metal

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strap(s) can electrically connect the pair of vertical field effect transistors to adjacent pair(s) of vertical field effect transistors. Also disclosed herein are methods of forming such semiconductor structures.

More particularly, disclosed herein is a semiconductor structure comprising at least a pair of vertical field effect transistors formed from an essentially U-shaped semiconductor body. That is, the semiconductor structure can comprise a U-shaped semiconductor body. This U-shaped semiconductor body can comprise a horizontal section, a first vertical section and a second vertical section. The horizontal section can comprise a shared source/drain region for the pair of vertical field effect transistors. The first vertical section can extend vertically from a first end of the horizontal section and can comprise, for a first vertical field effect transistor in the pair, a first channel region and a first source/drain region above the first channel region. The second vertical section can be parallel to the first vertical section, can extend vertically from a second end of the horizontal section opposite the first end, and can comprise, for a second vertical field effect transistor in the pair, a second channel region and a second source/drain region above the second channel region.

The semiconductor structure can further comprise multiple gates. Specifically, the semiconductor structure can comprise a first gate for the first vertical field effect transistor adjacent to the first vertical section at the first channel region and a second gate for the second vertical field effect transistor adjacent to the second vertical section at the second channel region. In this semiconductor structure, the first gate and the second gate can comprise multi-layered spacers on vertical surfaces of the first and second vertical sections. Each multi-layered spacer can comprise a gate dielectric layer and a gate conductor layer positioned laterally adjacent to the gate dielectric layer. Optionally, the first gate can, for example, wrap entirely around the first vertical section at the first channel region and the second gate can, for example, wrap entirely around the second vertical section at the second channel region. A relatively thin layer of dielectric material on the top surface of the horizontal section can electrically isolate the first and second gates from the shared source/drain region contained therein.

The semiconductor structure can further comprise a shared source/drain region contact, which is positioned laterally between and electrically isolated from the first and second gates and which extends vertically to a center portion of the horizontal section (i.e., to the shared source/drain region). Additional source/drain contacts can extend vertically to the first and second source/drain regions at the top of the first and second vertical sections of the semiconductor body. Alternatively, metal strap(s) at the top of the first and/or second vertical sections can electrically connect the pair of vertical field effect transistors and, particularly, the first and/or second source/drain regions of the first and/or second vertical field effect transistors in the pair to adjacent pair(s) of vertical field effect transistors.

In the semiconductor structure described above, an exemplary configuration is discussed wherein the first and second gates wrap entirely around the first and second channel regions in the first and second vertical sections, respectively, of the semiconductor body. However, it should be understood that alternative gate configurations could be used. For example, in another semiconductor structure disclosed herein, discrete front and back gates can be positioned on opposing vertical surfaces of the first and second vertical sections of the semiconductor body.

Specifically, this semiconductor structure can similarly comprise a U-shaped semiconductor body. This semiconduc-

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tor body can comprise a horizontal section, a first vertical section and a second vertical section. The horizontal section can comprise a shared source/drain region for the pair of vertical field effect transistors. The first vertical section can extend vertically from a first end of the horizontal section, can have first opposing vertical surfaces, and can comprise, for a first vertical field effect transistor in the pair, a first channel region and a first source/drain region above the first channel region. The second vertical section can be parallel to the first vertical section, can extend vertically from a second end of the horizontal section opposite the first end, can have second opposing vertical surfaces, and can comprise, for a second vertical field effect transistor in the pair, a second channel region and a second source/drain region above the second channel region.

The semiconductor structure can further comprise multiple gates. Specifically, the semiconductor structure can comprise first gates adjacent to the first opposing vertical surfaces of the first vertical section at the first channel region and second gates adjacent to the second opposing vertical surfaces of the second vertical section at the second channel region. The first gates can comprise a first front gate above the horizontal section and a first back gate opposite the first front gate. Similarly, the second gates can comprise a second front gate above the horizontal section and a second back gate opposite the second front gate. A relatively thin layer of dielectric material on the top surface of the horizontal section can electrically isolate the first and second front gates from the shared source/drain region contained therein.

The semiconductor structure can further comprise a shared source/drain region contact, which is positioned laterally between and electrically isolated from the first and second front gates and which extends vertically to a center portion of the horizontal section (i.e., to the shared source/drain region). Additional source/drain contacts can extend vertically to the first and second source/drain regions at the top of the first and second vertical sections of the semiconductor body. Alternatively, metal strap(s) at the top of the first and/or second vertical sections can electrically connect the pair of vertical field effect transistors and, particularly, the first and/or second source/drain regions of the first and/or second vertical field effect transistors in the pair to adjacent pair(s) of vertical field effect transistors.

Also disclosed herein are methods of forming such semiconductor structures. For example, one method of forming a semiconductor structure can comprise forming a pair of vertical field effect transistors. To form the pair, an essentially U-shaped semiconductor body can be formed such that it comprises a horizontal section, a first vertical section that extends vertically from a first end of the horizontal section and a second vertical section that is parallel to the first vertical section and that extends vertically from a second end of the horizontal section opposite the first end. For example, to form this semiconductor body, a mandrel can be formed on a semiconductor layer and sidewall spacers can be formed on opposing sidewalls of the mandrel. As a result, the semiconductor layer will have a masked portion, which is aligned below the mandrel and the sidewall spacers and which is positioned laterally between unmasked portions. The unmasked portions of the semiconductor layer can be removed and, then, the mandrel can be removed. Following removal of the mandrel, an exposed portion of the semiconductor layer between the sidewall spacers can be etched back, thereby forming the first vertical section, the second vertical section and the horizontal section between the first vertical section and the second vertical section.

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After the semiconductor body is formed, the sidewall spacers can be removed and a dielectric material can be deposited over the semiconductor body. The dielectric material can be etched back to expose vertical surfaces of the first vertical section and the second vertical section without exposing the top surface of the horizontal section. That is, this etch back process can be performed such that the horizontal section between the first vertical section and the second vertical section remains covered by a relatively thin layer of the dielectric material.

Next, a first gate can be formed adjacent to the first vertical section and a second gate can be formed adjacent to the second vertical section. For example, the first and second gates can be formed such that each gate comprises a multi-layered spacer comprising a gate dielectric layer and a gate conductor layer positioned laterally adjacent to the gate dielectric layer. The first and second gates can further each be formed so as to wrap around the first vertical section and the second vertical section, respectively.

It should be noted that before and/or in between the above-described processes, various doping processes can be performed so that in the resulting semiconductor structure, the horizontal section comprises a shared source/drain region for the pair of vertical field effect transistors, so that the first vertical section comprises, for a first vertical field effect transistor of the pair, a first channel region and a first source/drain region above the first channel region, and so that the second vertical section comprises, for a second vertical field effect transistor of the pair, a second channel region and a second source/drain region above the second channel region.

Subsequently, contact(s) and, optionally, metal strap(s) can be formed. Specifically, a shared source/drain contact can be formed such that it is positioned laterally between and electrically isolated from the first and second gates and such that it extends vertically to the shared source/drain region for the pair of vertical field effect transistors at the center portion of the horizontal section of the semiconductor body. Additional source/drain contacts can also be formed that extend vertically to the first and second source/drain regions of the first and second vertical field effect transistors at the top of the first and second vertical sections of the semiconductor body. Alternatively, metal strap(s) can be formed at the top of the first and/or second vertical sections to electrically connect the pair of vertical field effect transistors and, particularly, the first and/or second source/drain regions of the first and/or second vertical field effect transistors in the pair to adjacent pair(s) of vertical field effect transistors.

In the method described above, exemplary process steps are discussed wherein the first and second gates are formed so as to wrap entirely around the first and second vertical sections, respectively, of the semiconductor body. However, it should be understood that alternative and/or additional process steps could be performed to achieve semiconductor structures with alternative gate configurations.

For example, another method disclosed herein similarly comprises forming a pair of vertical field effect transistors by forming an essentially U-shaped semiconductor body. In this case, a mandrel can be formed on a semiconductor layer and sidewall spacers can be formed on opposing sidewalls of the mandrel. As a result, the semiconductor layer will have a masked portion, which is aligned below the mandrel and the sidewall spacers and which is positioned laterally between unmasked portions. The unmasked portions can be removed and, then, a dielectric material can be deposited.

After the dielectric material is deposited, openings can be formed (e.g., patterned and etched) such that they extend vertically through the dielectric material and such that the

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masked portion is positioned laterally between the openings. These openings can then be filled with a conductor such that the masked portion will, as a result, be positioned laterally between a first back gate and a second back gate. Then, the mandrel can be removed and the exposed portion of the semiconductor layer between the sidewall spacers can be etched back to form the essentially U-shaped semiconductor body, which comprises a horizontal section, a first vertical section extending vertically from a first end of the horizontal section and having first opposing vertical surfaces, and a second vertical section parallel to the first vertical section, extending vertically from a second end of the horizontal section opposite the first end, and having second opposing vertical surfaces.

After the semiconductor body is formed, the sidewall spacers can be removed and an additional dielectric material can be deposited over the semiconductor body. The additional dielectric material between the first vertical section and the second vertical section can then be etched back to expose a first vertical surface of the first vertical section and a second vertical surface of the second vertical section without exposing the horizontal section. That is, this etch back process can be performed such that the inner vertical surfaces of the first and second vertical sections of the semiconductor body are exposed and further such that the horizontal section between the first vertical section and the second vertical section remains covered by a relatively thin layer of the additional dielectric material.

Next, front gates can be formed adjacent to the exposed inner vertical surfaces of the first and second vertical sections. Specifically, a first front gate can be formed adjacent to the first vertical surface of the first vertical section opposite the first back gate and a second front gate can be formed adjacent to the second vertical surface of the second vertical section opposite the second back gate.

It should be noted that before and/or in between the above-described processes, various doping processes can be performed so that in the resulting semiconductor structure, the horizontal section comprises a shared source/drain region for a pair of vertical field effect transistors, so that the first vertical section comprises, for a first vertical field effect transistor of the pair, a first channel region and a first source/drain region above the first channel region, and so that the second vertical section comprises, for a second vertical field effect transistor of the pair, a second channel region and a second source/drain region above the second channel region.

Subsequently, contact(s) and, optionally, metal strap(s) can be formed. Specifically, a shared source/drain contact can be formed such that it is positioned laterally between and electrically isolated from the first and second gates and such that it extends vertically to the shared source/drain region for the pair of vertical field effect transistors at the center portion of the horizontal section of the semiconductor body. Additional source/drain contacts can also be formed that extend vertically to the first and second source/drain regions of the first and second vertical field effect transistors at the top of the first and second vertical sections of the semiconductor body. Alternatively, metal strap(s) can be formed at the top of the first and/or second vertical sections to electrically connect the pair of vertical field effect transistors and, particularly, the first and/or second source/drain regions of the first and/or second vertical field effect transistors in the pair to adjacent pair(s) of vertical field effect transistors.

#### BRIEF DESCRIPTION OF THE DRAWINGS

The embodiments herein will be better understood from the following detailed description with reference to the drawings, which are not necessarily drawn to scale and in which:

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FIG. 1A is a cross-section diagram illustrating a semiconductor structure comprising pair(s) of vertical field effect transistors;

FIG. 1B is a top view diagram illustrating the semiconductor structure of FIG. 1A;

FIG. 2A is a cross-section diagram illustrating another semiconductor structure comprising pair(s) of vertical field effect transistors;

FIG. 2B is a top view diagram illustrating the semiconductor structure of FIG. 1A;

FIG. 3 is a flow diagram illustrating a method of forming the semiconductor structure of FIGS. 1A-1B;

FIG. 4 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 5 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 6 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 7 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 8 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 9 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 10A is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 10B is a top view diagram illustrating the partially completed semiconductor structure of FIG. 10A;

FIG. 11 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 3;

FIG. 12 is a flow diagram illustrating a method of forming the semiconductor structure of FIGS. 2A-2B;

FIG. 13 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 14 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 15 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 16 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 17 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 18 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 19 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 20 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 21 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 22 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 23 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 24A is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12;

FIG. 24B is a top view diagram illustrating the partially completed semiconductor structure of FIG. 24A; and,

FIG. 25 is a cross-section diagram illustrating a partially completed semiconductor structure formed according to the method of FIG. 12.

#### DETAILED DESCRIPTION

As mentioned above, integrated circuit design decisions are often driven by device scalability, manufacturing efficiency and costs. For example, size scaling of single-gate planar field effect transistors (FETs) resulted in devices with a smaller channel length. Unfortunately, the smaller channel length resulted in a corresponding increase in short channel effects and a decrease in drive current. In response, different types of multi-gate non-planar field effect transistors (MUGFETs), such as dual-gate non-planar FETs (also referred to herein as fin-type FETs (FINFETs)) and tri-gate non-planar FETs, which comprise one or more semiconductor fins, were developed in order to provide reduced-size field effect transistors, while simultaneously avoiding corresponding increases in short channel effects and decreases in drive current. Unfortunately, further size scaling of conventional MUGFETs has been limited by the required specifications for the different features of such devices. For example, a minimum gate length is required in order to switch a MUGFET on and off. This minimum gate length must, in turn, be considered in setting the pitch between source/drain contacts. Additionally, in MUGFETs that incorporate multiple semiconductor fins to increase transistor width and, thereby drive current, the pitch between semiconductor fins must be sufficiently large so as to allow for deposition of gate material between the semiconductor fins. Finally, the thickness of the semiconductor layer used to form the MUGFET must be equal to the height of the semiconductor fin(s).

In view of the foregoing, disclosed herein are semiconductor structures configured to allow for continued size scaling of field effect transistors. The semiconductor structures each comprise a pair of vertical field effect transistors formed from an essentially U-shaped semiconductor body. This semiconductor body has a horizontal section and first and second vertical sections. The horizontal section can comprise a shared source/drain region for first and second vertical field effect transistors. The first and second vertical sections can each comprise a channel region and a source/drain region above the channel region for the first and second vertical field effect transistors, respectively. In one semiconductor structure, each vertical section has a gate wrapped around the channel region. In another semiconductor structure, each vertical section has a front gate positioned adjacent to the inner vertical surface at the channel region and a back gate positioned adjacent to the outer vertical surface at the channel region. In any case, a contact, which is electrically isolated from the gates, can extend vertically to the shared source/drain region in the horizontal section. Optionally, metal strap(s) can electrically connect the pair of vertical field effect

transistors to adjacent pair(s) of vertical field effect transistors. Also disclosed herein are methods of forming such semiconductor structures.

More particularly, referring to FIGS. 1A-1B, disclosed herein is a semiconductor structure 100. This semiconductor structure 100 can comprise at least one pair 161-162 of vertical field effect transistors 121-122. For purposes of illustration, two pairs of vertical field effect transistors are shown; however, it should be understood that the semiconductor structure 100 could comprise any number of one or more pairs of vertical field effect transistors. It should be understood that the term vertical field effect transistor refers to a field effect transistor in which a channel region is stacked vertically between source/drain regions (i.e., in which a channel region is on top of a source/drain region and another source/drain region is on top of the channel region) as opposed to being positioned laterally between the source/drain regions.

Each pair (e.g., pair 161) of vertical field effect transistors can be formed using an essentially U-shaped semiconductor body 110. Specifically, the U-shaped semiconductor body 110 can be positioned above and immediately adjacent to an insulator layer 102 (e.g., a buried oxide (BOX) layer or other suitable insulator layer) on a semiconductor substrate 101 (e.g., on a silicon substrate or any other suitable semiconductor substrate) (as shown). Alternatively, the U-shaped semiconductor body 110 can be formed from an upper portion of a bulk semiconductor substrate (e.g., a bulk silicon substrate or any other suitable bulk semiconductor substrate) and electrically isolated from a lower portion of the bulk semiconductor substrate by a buried well region (not shown).

In any case, the U-shaped semiconductor body 110 can comprise a horizontal section 111 (e.g., immediately adjacent to the insulator layer 102), a first vertical section 112a that extends vertically from a first end of the horizontal section 111, and a second vertical section 112b that extends vertically from a second end of the horizontal section 111 opposite the first end such that the first vertical section 112a and second vertical section 112b are parallel. The horizontal section 111 can comprise a shared source/drain region 130 for the pair 161 of vertical field effect transistors 121-122. The first vertical section 112a can comprise, for a first vertical field effect transistor 121 in the pair 161, a first channel region 151 adjacent to the shared source/drain region 130 in the horizontal section 111 and a first source/drain region 131 above the first channel region 151. The second vertical section 112b can be parallel to the first vertical section 112a and can comprise, for a second vertical field effect transistor 122 in the pair 161, a second channel region 152 adjacent to the shared source/drain region 130 in the horizontal section 111 and a second source/drain region 132 above the second channel region 152. Thus, for example, the lower portion of the first and second vertical sections 112a-b containing the first and second channel regions 151-152, respectively, can have a first type conductivity (e.g., P-type conductivity), whereas the horizontal section 111 containing the shared source/drain region 130 as well as the upper portions of the first and second vertical sections 112a-b containing the first and second source/drain regions 131-132 can have a second type conductivity (e.g., N-type conductivity) that is different from the first type conductivity.

Optionally, the horizontal and/or vertical sections of the U-shaped semiconductor body 110 can comprise one or more additional doped regions (not shown) including, but are not limited to, source/drain extension regions and/or halo regions between the first and second channel regions 151-152 and the

shared source/drain region **130** and/or between the first and second channel regions **151-152** and the first and second source/drain regions **131-132**.

Optionally, the U-shaped semiconductor body **110** can comprise a single type of monocrystalline semiconductor material (e.g., silicon or any other suitable monocrystalline semiconductor material). Alternatively, the U-shaped semiconductor body **110** can comprise multiple different types of monocrystalline semiconductor materials. For example, during processing as discussed in greater detail below with regard to the methods, the semiconductor body **110** may be etched from a single semiconductor layer such that it comprises a single semiconductor material. Alternatively, it can be etched from a stack of multiple semiconductor layers such that it comprises different semiconductor materials at different levels. Thus, the horizontal section **111** containing the shared source/drain region **130**, the lower portion of the first and second vertical sections **112a-b** containing the first and second channel regions **151-152** and/or the upper portion of the first and second vertical sections **112a-b** containing the first and second source/drain regions **131-132** can comprise different types of semiconductor materials (e.g., silicon, silicon germanium, silicon germanium carbide, etc.). Those skilled in the art will recognize that different types of semiconductor materials can be used in different components of field effect transistors to tailor strain in the channel region.

One or more layers of dielectric material **171** (e.g., silicon dioxide, silicon nitride, etc.) can laterally surround the outer edges of the horizontal section **111** and a relatively thin portion **172** of the layer(s) of dielectric material **171** can cover the top surface of the horizontal section **111** between the first and second vertical sections **112a-b**.

The semiconductor structure **100** can further comprise multiple gates. Specifically, the semiconductor structure **100** can comprise a first gate **141** for the first vertical field effect transistor **121** on the layer(s) of dielectric material **171** positioned laterally adjacent to a first vertical surface of the first vertical section **112a** at the first channel region **151** and a second gate **142** for the second vertical field effect transistor **122** on the layer(s) of dielectric material **171** and positioned laterally adjacent to a second vertical surface of the second vertical section **112b** at the second channel region **152**. The first gate **141** and the second gate **142** can comprise, for example, multi-layered spacers. Each multi-layered spacer can comprise a gate dielectric layer **143** immediately adjacent to the vertical surface of the vertical section and a gate conductor layer **144** positioned laterally adjacent to the gate dielectric layer **143**. The gate dielectric layer **143** can comprise, for example, a silicon dioxide layer, a silicon nitride layer, a silicon oxynitride layer, or any other suitable gate dielectric including, but not limited to, a high-K gate dielectric layer such as a hafnium (Hf)-based gate dielectric layer (e.g., hafnium oxide, hafnium silicon oxide, hafnium silicon oxynitride, hafnium aluminum oxide, etc.) or some other suitable high-K gate dielectric layer (e.g., aluminum oxide, tantalum oxide, zirconium oxide, etc.). The gate conductor layer **144** can comprise, for example, a doped polysilicon gate conductor layer, a metal gate conductor layer or any other suitable gate conductor layer.

It should be understood that, although a single gate dielectric layer **143** and a single gate conductor layer **144** are illustrated in each of the first gate **141** and second gate **142** of FIG. **1A**, the gate dielectric layer **143** can comprise a stack of multiple gate dielectric materials and the gate conductor layer **144** can similarly comprise a stack of different gate conductor materials and these different gate conductor materials may vary depending upon the conductivity type of the field effect

transistor. For example, for an N-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having an N-type work function that is between about 3.9 eV and about 4.2 eV (i.e., an N-type metal gate conductor). Exemplary N-type metal gate conductors can comprise hafnium, zirconium, titanium, tantalum, aluminum, and alloys thereof, such as, hafnium carbide, zirconium carbide, titanium carbide, tantalum carbide, and aluminum carbide. For a P-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having a P-type work function that is between about 4.9 eV and about 5.2 eV (i.e., a P-type metal gate conductor). Exemplary P-type metal gate conductors include, for example, ruthenium, palladium, platinum, cobalt, and nickel, as well as metal oxides (aluminum carbon oxide, aluminum titanium carbon oxide, etc.) and metal nitrides (e.g., titanium nitride, titanium silicon nitride, tantalum silicon nitride, titanium aluminum nitride, tantalum aluminum nitride, etc.).

Optionally, the first gate **141** can wrap entirely around the first vertical section **112a** at the first channel region **151** and the second gate **142** can wrap entirely around the second vertical section **112b** at the second channel region **152**. In this case, the portion **172** of the layer(s) of dielectric material **171** on the top surface of the horizontal section **111** can electrically isolate the first and second gates **141-142** from the shared source/drain region **130**.

It should be noted that, as illustrated in FIG. **1B**, the gate conductor layer **144** can have a first thickness **191** on the opposing sides of the first and second vertical sections **112a-b** and a second thickness **192** that is different from the first thickness on the opposing ends of the vertical sections **112a-b**. This second thickness **192** can be relatively large as compared to the first thickness **191** so as to allow for landing of gate contacts **183** on the first and second gates **141-142** at one or both ends of the vertical sections **112a-b** (i.e., to allow the gates **141-142** to be properly contacted).

Optionally, the semiconductor structure **100** can comprise silicide layers **190** on the top surfaces of the first and second vertical sections **112a-b** and/or the center portion of the horizontal section **111**. The silicide layer(s) **190** can comprise, for example, a silicide of a refractory or noble metal (e.g., nickel (Ni), cobalt (Co), tungsten (W), chromium (Cr), platinum (Pt), titanium (Ti), molybdenum (Mo), palladium (Pd), etc.) or an alloy thereof. As discussed in detail below with regard to the methods, the process of forming the silicide layer **190** on the top surface of the center portion of the horizontal section **111** can, depending upon the thickness of the horizontal section **111**, consume that entire center portion such that the shared source/drain region **130** is divided into two discrete sections separated by the silicide layer **190**.

The semiconductor structure **100** can further comprise one or more layers of interlayer dielectric material **173** (e.g., silicon dioxide, silicon nitride, borophosphosilicate glass (BPSG), etc.) on the dielectric material **171**, including on the portion **172** of dielectric material **171** between the first and second vertical sections **112a-b**, and further covering the first and second gates **141-142** and the upper portions of the first and second vertical sections **112a-b** that extend vertically above the level of the first and second gates **141-142**. Multiple contacts **181-183** can extend vertically through the interlayer dielectric material **173** to the different components of the pair **161** of vertical field effect transistors. Specifically, a shared source/drain region contact **181** can extend vertically through the interlayer dielectric material **173** such that it is positioned

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laterally between and electrically isolated from the first and second gates **141-142**. This contact **181** can further extend vertically through the thin portion **172** of the dielectric material **171** to the center portion of the horizontal section **111** below (i.e., to the shared source/drain region **130**). Additional source/drain contacts **182** can extend vertically through the interlayer dielectric material **173** to the first and second source/drain regions **131-132** at the top of the first and second vertical sections **112a-b** of the semiconductor body **110**. Gate contacts **183** can extend vertically through the interlayer dielectric material **173** to the first and second gates **141-142**. Such contacts **181-183** can be non-self-aligned (as shown) or self-aligned. Self-aligned contacts are well known in the art and, thus, the details thereof are omitted from this specification in order to allow the reader to focus on the salient aspects of the disclosure. Optionally, rather than simply contacting the first and second source/drain regions **131-132**, metal strap(s) **184** (i.e., wire(s), local interconnect(s), etc.) can be formed in the interlayer dielectric material **173** at the top of the first and/or second vertical sections **112a-b** in order to electrically connect the first and/or second source/drain regions **131-132** of the first and/or second vertical field effect transistors **121-122** in the pair **161** to adjacent pair(s) (e.g., additional pair **162**) of vertical field effect transistors.

In the semiconductor structure **100** described above and illustrated in FIGS. **1A-1B**, an exemplary configuration is discussed wherein the first and second gates **140-141** wrap entirely around the first and second channel regions **151-152** in the first and second vertical sections **112a-b**, respectively, of the U-shaped semiconductor body **110**. However, it should be understood that alternative gate configurations could be used. For example, in another semiconductor structure **200** as shown in FIGS. **2A-2B**, discrete front and back gates can be positioned on opposing vertical surfaces of the first and second vertical sections of the U-shaped semiconductor body.

Specifically, referring to FIGS. **2A-2B**, disclosed herein is a semiconductor structure **200**. This semiconductor structure **200** can comprise at least one pair **261-262** of vertical field effect transistors **221-222**. For purposes of illustration, two pairs of vertical field effect transistors are shown; however, it should be understood that the semiconductor structure **100** could comprise any number of one or more pairs of vertical field effect transistors.

Each pair (e.g., pair **261**) of vertical field effect transistors can be formed using an essentially U-shaped semiconductor body **210**. Specifically, the U-shaped semiconductor body **210** can be positioned above and immediately adjacent to an insulator layer **202** (e.g., a buried oxide (BOX) layer or other suitable insulator layer) on a semiconductor substrate **201** (e.g., on a silicon substrate or any other suitable semiconductor substrate) (as shown). Alternatively, the U-shaped semiconductor body **210** can be formed from an upper portion of a bulk semiconductor substrate (e.g., a bulk silicon substrate or any other suitable bulk semiconductor substrate) and electrically isolated from a lower portion of the bulk semiconductor substrate by a buried well region (not shown).

In any case, the U-shaped semiconductor body **210** can comprise a horizontal section **211** (e.g., immediately adjacent to the insulator layer **202**), a first vertical section **212a** that extends vertically from a first end of the horizontal section **211** and has first opposing vertical surfaces, and a second vertical section **212b** that extends vertically from a second end of the horizontal section **211** opposite the first end and has second opposing vertical surfaces. Thus, the first vertical section **211a** and the second vertical section **212b** are parallel. The horizontal section **211** can comprise a shared source/drain region **230** for the pair **261** of vertical field effect tran-

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sistors **221-222**. The first vertical section **212a** can comprise, for a first vertical field effect transistor **221** in the pair **261**, a first channel region **251** adjacent to the shared source/drain region **230** in the horizontal section **211** and a first source/drain region **231** above the first channel region **251**. The second vertical section **212b** can be parallel to the first vertical section **212a** and can comprise, for a second vertical field effect transistor **222** in the pair **261**, a second channel region **252** adjacent to the shared source/drain region **230** in the horizontal section **211** and a second source/drain region **232** above the second channel region **252**. Thus, for example, the lower portion of the first and second vertical sections **212a-b** containing the first and second channel regions **251-252**, respectively, can have a first type conductivity (e.g., P-type conductivity), whereas the horizontal section **211** containing the shared source/drain region **230** as well as the upper portions of the first and second vertical sections **212a-b** containing the first and second source/drain regions **231-232** can have a second type conductivity (e.g., N-type conductivity) that is different from the first type conductivity.

Optionally, the horizontal and/or vertical sections of the U-shaped semiconductor body **210** can comprise one or more additional doped regions (not shown) including, but are not limited to, source/drain extension regions and/or halo regions between the first and second channel regions **251-252** and the shared source/drain region **230** and/or between the first and second channel regions **251-252** and the first and second source/drain regions **231-232**.

Optionally, the U-shaped semiconductor body **210** can comprise a single type of monocrystalline semiconductor material (e.g., silicon or any other suitable monocrystalline semiconductor material). Alternatively, the U-shaped semiconductor body **210** can comprise multiple different types of monocrystalline semiconductor materials. For example, during processing as discussed in greater detail below with regard to the methods, the semiconductor body **210** may be etched from a single semiconductor layer such that it comprises a single semiconductor material. Alternatively, it can be etched from a stack of multiple semiconductor layers such that it comprises different semiconductor materials at different levels. Thus, the horizontal section **211** containing the shared source/drain region **230**, the lower portion of the first and second vertical sections **212a-b** containing the first and second channel regions **251-252** and/or the upper portion of the first and second vertical sections **212a-b** containing the first and second source/drain regions **231-232** can comprise different types of semiconductor materials (e.g., silicon, silicon germanium, silicon germanium carbide, etc.). Those skilled in the art will recognize that different types of semiconductor materials can be used in different components of field effect transistors in order to tailor strain in the channel region.

One or more layers of dielectric material **271** (e.g., silicon dioxide, silicon nitride, etc.) can laterally surround the outer edges of the horizontal section **211** and a relatively thin layer of additional dielectric material **272** (e.g., silicon dioxide, silicon nitride, etc.) can cover the top surface of the horizontal section **211** between the first and second vertical sections **212a-b**.

The semiconductor structure **200** can further comprise multiple gates. Specifically, the semiconductor structure can comprise first gates (i.e., a first front gate **241** and a first back gate **245**) for the first vertical field effect transistors **221** adjacent to the first opposing vertical surfaces of the first vertical section **212a** at the first channel region **251** and second gates (i.e., a second front gate **242** and a second back gate **246**) for the second vertical field effect transistors **222** adja-



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cent to the second opposing vertical surfaces of the second vertical section **212b** at the second channel region **252**.

The first front gate **241** can be positioned on the layer of additional dielectric material **272** above the horizontal section **211** and positioned laterally adjacent to a first vertical surface of the first vertical section **212a** at the first channel region **251** and the second front gate **242** can also be positioned on the layer of additional dielectric material **272** above the horizontal section **211** and positioned laterally adjacent to a second vertical surface of the second vertical section **212b** at the second channel region **252**. The first front gate **241** and the second front gate **242** can comprise, for example, multi-layered spacers. Each multi-layered spacer can comprise a gate dielectric layer **243** immediately adjacent to a vertical surface of a vertical section and a gate conductor layer **244** positioned laterally adjacent to the gate dielectric layer **243**. The gate dielectric layer **243** can comprise, for example, a silicon dioxide layer, a silicon nitride layer, a silicon oxynitride layer, or any other suitable gate dielectric layer including, but not limited to, a high-K gate dielectric layer such as a hafnium (Hf)-based gate dielectric layer (e.g., hafnium oxide, hafnium silicon oxide, hafnium silicon oxynitride, hafnium aluminum oxide, etc.) or some other suitable high-K gate dielectric layer (e.g., aluminum oxide, tantalum oxide, zirconium oxide, etc.). The gate conductor layer **244** can comprise, for example, doped polysilicon gate conductor layer, a metal gate conductor layer or any other suitable gate conductor layer.

It should be understood that, although a single gate dielectric layer **243** and a single gate conductor layer **244** are illustrated in each of the first front gate **241** and second front gate **242** of FIG. 2A, the gate dielectric layer **243** can comprise a stack of multiple gate dielectric materials and the gate conductor layer **244** can similarly comprise a stack of different gate conductor materials and these different gate conductor materials may vary depending upon the conductivity type of the field effect transistor. For example, for an N-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having an N-type work function that is between about 3.9 eV and about 4.2 eV (i.e., an N-type metal gate conductor). Exemplary N-type metal gate conductors can comprise hafnium, zirconium, titanium, tantalum, aluminum, and alloys thereof, such as, hafnium carbide, zirconium carbide, titanium carbide, tantalum carbide, and aluminum carbide. For a P-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having a P-type work function that is between about 4.9 eV and about 5.2 eV (i.e., a P-type metal gate conductor). Exemplary P-type metal gate conductors include, for example, ruthenium, palladium, platinum, cobalt, and nickel, as well as metal oxides (aluminum carbon oxide, aluminum titanium carbon oxide, etc.) and metal nitrides (e.g., titanium nitride, titanium silicon nitride, tantalum silicon nitride, titanium aluminum nitride, tantalum aluminum nitride, etc.).

It should be noted that, as illustrated in FIG. 2B, the gate conductor layer **244** of the first front gate **241** and the second front gate **242** can wrap around the opposing ends of the first and second vertical sections **212a-b**. This gate conductor layer **244** can have a first thickness **291** on one side of each of the first and second vertical sections **212a-b** and a second thickness **292** that is different from the first thickness on the opposing ends of the first and second vertical sections **212a-b**. This second thickness **292** can be relatively large as compared to the first thickness **291** so as to allow for landing of gate

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contacts **283** on the first and second front gates **241-242** at one or both ends of the first and second vertical sections **212a-b** (i.e., to allow the first and second front gates **241-242** to be properly contacted).

The first back gate **245** can be positioned on a first vertical surface of the first vertical section **212a** at the first channel region **251** and opposite the first front gate **241**. Similarly, the second back gate **246** can be positioned on a second vertical surface of the second vertical section **212b** at the second channel region **252** and opposite the second front gate **242**. The first back gate **245** and second back gate **246** can each comprise opening, which extends vertically through the one or more layer(s) of dielectric material **271** below the level of the horizontal section **211** (e.g., through the insulator layer **202** and into the semiconductor substrate **201**) and which is filled with a conductor **248** (also referred to herein as a conductive plate). The conductive plate **248** can comprise one or more conductive layers of a metal (e.g., copper, tungsten, aluminum or any other suitable metal), a metal alloy, or doped polysilicon. In this case, the portions of the one or more layer(s) of dielectric material **271** between each conductive plate **248** and the first and second vertical sections **212a-b** will function as a gate dielectric **247** for the first and second back gates **245-246**, respectively.

Optionally, the semiconductor structure **200** can comprise silicide layers **290** on the top surfaces of the first and second vertical sections **212a-b** and/or the center portion of the horizontal section **211**. The silicide layer(s) **290** can comprise, for example, a silicide of a refractory or noble metal (e.g., nickel (Ni), cobalt (Co), tungsten (W), chromium (Cr), platinum (Pt), titanium (Ti), molybdenum (Mo), palladium (Pd), etc.) or an alloy thereof. As discussed in detail below with regard to the methods, the process of forming the silicide layer **290** on the top surface of the center portion of the horizontal section **211** can, depending upon the thickness of the horizontal section **211**, consume that entire center portion such that the shared source/drain region **230** is divided into two discrete sections separated by the silicide layer **290**.

The semiconductor structure **200** can further comprise one or more layer(s) of interlayer dielectric material **273** (e.g., silicon dioxide, silicon nitride, borophosphosilicate glass (BPSG), etc.) on the dielectric material **271**, on the thin layer of additional dielectric material **272** between the first and second vertical sections **212a-b**, and further covering the first and second front gates **241-242**, the upper portions of the first and second vertical sections **212a-b** that extend vertically above the level of the first and second front gates **241-242**. Multiple contacts **281-283** can extend vertically to the different components of the pair **261** of vertical field effect transistors. Specifically, a shared source/drain region contact **281** can extend vertically through the interlayer dielectric material **273** such that it is positioned laterally between and electrically isolated from the first and second gates **241-242**. This contact **281** can further extend vertically through the layer of additional dielectric material **272** to a center portion of the horizontal section **211** below (i.e., to the shared source/drain region **230**). Additional source/drain contacts **282** can extend vertically through the interlayer dielectric material **273** to the first and second source/drain regions **231-232** at the top of the first and second vertical sections **212a-b** of the semiconductor body **210**. Gate contacts **283** can extend vertically through the interlayer dielectric material **273** to the first and second front gates **241-242**. Such contacts **281-283** can be non-self-aligned (as shown) or self-aligned. Self-aligned contacts are well known in the art and, thus, the details thereof are omitted from this specification in order to allow the reader to focus on the salient aspects of the disclosure. Alternatively, rather than

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simply contacting the source/drain regions **231-232**, metal strap(s) **284** (i.e., wire(s), local interconnect(s), etc.) at the top of the first and/or second vertical sections **212a-b** can electrically connect the first and/or second source/drain regions **231-232** of the first and/or second vertical field effect transistors **221-222** in the pair **261** to adjacent pair(s) (e.g., additional pair **262**) of vertical field effect transistors.

Also disclosed herein are methods of forming such semiconductor structures **100, 200**. For example, referring to FIG. **3**, one method of forming a semiconductor structure **100**, as illustrated in FIGS. **1A-1B**, can begin by providing a wafer (**302**). This wafer can comprise, for example, a semiconductor-on-insulator (SOI) wafer comprising a stack of one or more semiconductor layers **103** (see detailed discussion below) immediately adjacent to an insulator layer **102** (e.g., a buried oxide (BOX) layer or other suitable insulator layer) on a semiconductor substrate **101** (e.g., on a silicon substrate or any other suitable semiconductor substrate) (see FIG. **4**). Alternatively, the wafer can comprise a bulk semiconductor substrate with a buried well region, which can provide electrically isolation between upper and lower portions of the semiconductor substrate (not shown). For purposes of illustration, the processes required to form the semiconductor structure **100** will be described below and illustrated in the Figures with respect to an SOI wafer.

The method can further comprise forming at least one pair of vertical field effect transistors on the wafer (**304**). For purposes of illustration formation of the pair **161** shown in FIGS. **1A-1B** is described; however, it should be understood that one or more additional pairs of vertical field effect transistors (e.g., see pair **162**) could simultaneously be formed. To form a pair of vertical field effect transistors, such as the pair **161** in FIGS. **1A-1B**, an essentially U-shaped semiconductor body **110** must first be formed such that it comprises a horizontal section **111**, a first vertical section **112a** that extends vertically from a first end of the horizontal section **111** and a second vertical section **112b** that is parallel to the first vertical section **112a** and that extends vertically from a second end of the horizontal section **111** opposite the first end.

For example, to form this U-shaped semiconductor body **110**, a mandrel **104** can be formed on the semiconductor layer **103** and sidewall spacers **105** can be formed on opposing sidewalls of the mandrel **104** (**306-308**, see FIG. **5**). The mandrel **104** can be formed, for example, by depositing a mandrel material layer on the semiconductor layer **103**. The mandrel material layer can comprise, for example, a dielectric material, such as silicon dioxide, or any other suitable mandrel material that can be selectively etched over the semiconductor layer **103** below. The mandrel material layer can then be lithographically patterned and etched to form an essentially rectangular-shaped body (referred to herein as a mandrel) above the semiconductor layer **103**. Next, sidewall spacers **105** can be formed on the opposing sidewalls of the mandrel **104** using conventional sidewall spacer formation techniques. The sidewall spacers **105** can comprise, for example, another dielectric material, such as silicon nitride, or any other suitable spacer material that can be selectively etched over the semiconductor layer **103** below. It should be noted that the spacer material should specifically be selected so that the mandrel **104** can also be selectively etched over the sidewall spacers **105**. As a result of processes **306-308**, the semiconductor layer **103** will have a masked portion **501**, which is aligned below the mandrel **104** and the sidewall spacers **105** and which is positioned laterally between unmasked portions **502**.

The unmasked portions **502** of the semiconductor layer **103** can be removed (e.g., using an anisotropic reactive ion

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etch (RIE) process) (**310**, see FIG. **6**). Then, the mandrel **104** can be selectively removed (**312**, see FIG. **7**). Those skilled in the art will recognize that the etch process used to remove the mandrel **104** will depend upon the materials used for the mandrel **104**, the sidewall spacers **105** and the semiconductor layer **103**. Following removal of the mandrel **104** at process **312**, an exposed portion **106** of the previously masked portion **501** of the semiconductor layer **103** between the sidewall spacers **105** can be etched back some distance less than the full thickness of the semiconductor layer **103** (e.g., using an anisotropic RIE process), thereby forming the U-shaped semiconductor body **110** with the first vertical section **112a**, the second vertical section **112b** and the horizontal section **111** between the first vertical section **112a** and the second vertical section **112b** (**314**, see FIG. **8**).

As mentioned above, the wafer provided at process **302** can comprise a stack of one or more semiconductor layers **103** on an insulator layer **102**. If the wafer comprises only a single semiconductor layer, the U-shaped semiconductor body **110** will similarly comprise only a single semiconductor layer. However, alternatively, the wafer can comprise multiple different semiconductor layers **103** on the insulator layer **102**. In this case, the U-shaped semiconductor body **110** can be formed such the horizontal section **111**, the lower portion of the first and second vertical sections **112a-b** and/or the upper portion of the first and second vertical sections **112a-b** comprise different types of semiconductor materials (e.g., silicon, silicon germanium, silicon germanium carbide, etc.). Those skilled in the art will recognize that different types of semiconductor materials can be used in different components of field effect transistors to tailor strain in the channel region.

After the U-shaped semiconductor body **110** is formed at process **314**, the sidewall spacers **105** can be selectively removed. Those skilled in the art will recognize that the etch process used to remove the sidewall spacers **105** will depend upon the materials used for the sidewall spacers **105** and the semiconductor layer **103** below. Next, one or more layers of dielectric material **171** (e.g., silicon dioxide, silicon nitride, etc.) can be deposited over the semiconductor body **110** and planarized to expose the top surfaces of the first and second vertical sections **112a-b** (**316**). The dielectric material **171** can then be etched back (e.g., using a buffered hydrofluoric acid (BHF) wet etch process) to expose vertical surfaces of the first vertical section **112a** and the second vertical section **112b** (**318**, see FIG. **9**). It should be noted that this process **316** should be timed so that etching is stopped before the top surface of the horizontal section **111** is exposed. That is, this etch back process **316** should be performed such that the horizontal section **111** between the first vertical section **112a** and the second vertical section **112b** remains covered by a relatively thin portion **172** of the dielectric material **171**.

Next, multiple gates **141-142** can be formed (**320**, see FIG. **10A**). Specifically, a first gate **141** for the first vertical field effect transistor **121** can be formed on the dielectric material **172** and positioned laterally adjacent to a first vertical surface of the first vertical section **112a** and a second gate **142** for the second vertical field effect transistor **122** can be formed on the dielectric material **171** and positioned laterally adjacent to a second vertical surface of the second vertical section **112b**. The first gate **141** and the second gate **142** can each be formed so as to comprise, for example, multi-layered spacers. That is, a conformal gate dielectric layer **143** can be deposited such that it is immediately adjacent to the exposed vertical surfaces of the vertical sections **112a-b**. The gate dielectric layer **143** can comprise, for example, a silicon dioxide layer, a silicon nitride layer, a silicon oxynitride layer, or any other suitable gate dielectric layer including, but not limited to, a high-K

gate dielectric layer such as a hafnium (Hf)-based gate dielectric layer (e.g., hafnium oxide, hafnium silicon oxide, hafnium silicon oxynitride, hafnium aluminum oxide, etc.) or some other suitable high-K dielectric material (e.g., aluminum oxide, tantalum oxide, zirconium oxide, etc.). Next, a gate conductor layer **144** can be deposited on the gate dielectric layer **143**. The gate conductor layer **144** can comprise, for example, a polysilicon gate conductor layer, a metal gate conductor layer or any other suitable gate conductor layer.

It should be understood that, although a single gate dielectric layer **143** and a single gate conductor layer **144** are illustrated, the gate dielectric layer **143** can comprise a stack of multiple gate dielectric materials and the gate conductor layer **144** can similarly comprise a stack of different gate conductor materials and these different gate conductor materials may vary depending upon the conductivity type of the field effect transistor. For example, for an N-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having an N-type work function that is between about 3.9 eV and about 4.2 eV (i.e., an N-type metal gate conductor). Exemplary N-type metal gate conductors can comprise hafnium, zirconium, titanium, tantalum, aluminum, and alloys thereof, such as, hafnium carbide, zirconium carbide, titanium carbide, tantalum carbide, and aluminum carbide. For a P-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having a P-type work function that is between about 4.9 eV and about 5.2 eV (i.e., a P-type metal gate conductor). Exemplary P-type metal gate conductors include, for example, ruthenium, palladium, platinum, cobalt, and nickel, as well as metal oxides (aluminum carbon oxide, aluminum titanium carbon oxide, etc.) and metal nitrides (e.g., titanium nitride, titanium silicon nitride, tantalum silicon nitride, titanium aluminum nitride, tantalum aluminum nitride, etc.).

Next, an anisotropic spacer etch process can be performed to remove the gate materials from horizontal surfaces of the semiconductor body **110**, thereby creating multi-layered spacers positioned laterally adjacent to the vertical surfaces of the first and second vertical sections **112a-b**. It should be noted that this spacer etch process should be performed so that the upper portions of the first and second vertical sections **112a-b** are also exposed. As a result of the processes described above, the first gate **141** will wrap entirely around the first vertical section **112a** and the second gate **142** will wrap entirely around the second vertical section **112b**.

It should be noted that, if the gate conductor layer **144** of the multi-layered spacers formed as a result of the process steps described above is too narrow to receive a contact, then additional gate conductor deposition and lithographic patterning steps may be required to increase the thickness **192** of the gate conductor layer **144** on one or both of the opposing ends of the first and second vertical sections **112a-b** as compared to the thickness **191** of the gate conductor layer **144** on the opposing sides (as shown in FIG. **10B**).

At various times before, during (i.e., in between), and/or after the above-described processes **306-320**, various doping processes can be performed so that in the resulting semiconductor structure **100** and, particularly, in the resulting U-shaped semiconductor body **110**, the horizontal section **111** comprises a shared source/drain region **130** for the pair **161** of vertical field effect transistors, the first vertical section **112a** comprises, for the first vertical field effect transistor **121** in the pair **161**, a first channel region **151** adjacent to the shared source/drain region **130** in the horizontal section **111**

and a first source/drain region **131** above the first channel region **151** and, the second vertical section **112b** comprises, for the second vertical field effect transistor **122** in the pair **161**, a second channel region **152** adjacent to the shared source/drain region **130** in the horizontal section **111** and a second source/drain region **132** above the second channel region **152** (**322**, see FIG. **11**). Thus, for example, these doping processes **322** can be performed such that the lower portion of the first and second vertical sections **112a-b** containing the first and second channel regions **151-152**, respectively, can have a first type conductivity (e.g., P-type conductivity), whereas the horizontal section **111** containing the shared source/drain region **130** as well as the upper portions of the first and second vertical sections **112a-b** containing the first and second source/drain regions **131-132** can have a second type conductivity (e.g., N-type conductivity) that is different from the first type conductivity. Optionally, additional doping processes may be performed so that the horizontal and/or vertical sections of the U-shaped semiconductor body **110** comprise one or more additional doped regions (not shown) including, but are not limited to, source/drain extension regions and/or halo regions between the first and second channel regions **151-152** and the shared source/drain region **130** and/or between the first and second channel regions **151-152** and the first and second source/drain regions **131-132**.

Optionally, an opening can be formed in the thin portion **172** of dielectric material **171** on the horizontal section **111** (e.g., using lithographic patterning and etch techniques) and silicide layers **190** can be formed the exposed top surfaces of the first and second vertical sections **112a-b** and the center portion of the horizontal section **111** (**324**, see FIGS. **1A-1B**). The silicide layer(s) **190** can be formed using conventional processing techniques. For example, a layer of a refractory or noble metal (e.g., nickel (Ni), cobalt (Co), tungsten (W), chromium (Cr), platinum (Pt), titanium (Ti), molybdenum (Mo), palladium (Pd), etc.) or an alloy thereof can be conformally deposited over the structure and, specifically, onto the exposed semiconductor surfaces. Next, an anneal process can be performed. Any metal remaining present after the anneal process is performed can be selectively removed. It should be noted that this process **324** of forming the silicide layers **190** can, depending upon the thickness of the horizontal section **111**, consume the entire center portion of the horizontal section **111** such that the shared source/drain region **130** will be divided into two discrete sections separated by a silicide layer **190** (not shown).

After silicide formation, one or more layers of interlayer dielectric material **173** (e.g., silicon dioxide, silicon nitride, borophosphosilicate glass (BPSG), etc.) can be deposited (**326**). Next, multiple contacts **181-183** can be formed that extend vertically through the interlayer dielectric material **173** to the different components of the pair **161** of vertical field effect transistors (**328**). Specifically, a shared source/drain region contact **181** can be formed such that it extends vertically through the interlayer dielectric material **173** and further through the thin portion **172** of the dielectric material **171** to the center portion of the horizontal section **111** below (i.e., to the shared source/drain region **130**). Thus, this shared source/drain region contact **181** will be positioned laterally between and will be electrically isolated from the first and second gates **141-142**. Additional source/drain contacts **182** can be formed that extend vertically through the interlayer dielectric material **173** to the first and second source/drain regions **131-132** at the top of the first and second vertical sections **112a-b** of the semiconductor body **110**. Gate contacts **183** can be formed that extend vertically through the

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interlayer dielectric material **173** to the first and second gates **141-142**. Various techniques for forming either non-self-aligned contacts (as shown) and/or self-aligned contacts can be used at process **326** to form the contacts **181-183**. Contact formation techniques are well known in the art and, thus, the details are omitted from this specification in order to allow the reader to focus on the salient aspects of the disclosure. Optionally, rather than simply contacting the first and second source/drain regions **131-132**, metal strap(s) **184** (i.e., wire(s), local interconnect(s), etc.) can be formed in the interlayer dielectric material **173** at the top of the first and/or second vertical sections **112a-b** (e.g., using conventional damascene processing techniques) in order to electrically connect the first and/or second source/drain regions **131-132** of the first and/or second vertical field effect transistors **121-122** in the pair **161** to adjacent pair(s) (e.g., additional pair **162**) of vertical field effect transistors.

In the method described above and illustrated in the flow diagram of FIG. 3, exemplary process steps are discussed wherein the first and second gates **141-142** of the first and second vertical field effect transistors **121-122** in the pair **161** are formed so as to wrap entirely around the first and second vertical sections **112a-b**, respectively, of the U-shaped semiconductor body **110**. However, it should be understood that alternative and/or additional process steps could be performed to achieve semiconductor structures with alternative gate configurations (e.g., the semiconductor structure **200** of FIGS. 2A-2B).

For example, referring to FIG. 12, another method disclosed herein similarly comprises providing a wafer (**1202**). This wafer can comprise, for example, a semiconductor-on-insulator (SOI) wafer comprising a stack of one or more semiconductor layers **203** (see detailed discussion below) immediately adjacent to an insulator layer **202** (e.g., a buried oxide (BOX) layer or other suitable insulator layer) on a semiconductor substrate **201** (e.g., on a silicon substrate or any other suitable semiconductor substrate) (see FIG. 13). Alternatively, the wafer can comprise a bulk semiconductor substrate with a buried well region, which can provide electrically isolation between upper and lower portions of the semiconductor substrate (not shown). For purposes of illustration, the processes required to form the semiconductor structure **200** will be described below and illustrated in the Figures with respect to an SOI wafer.

The method can further comprise forming at least one pair of vertical field effect transistors on the wafer (**1204**). For purposes of illustration formation of the pair **261** shown in FIGS. 2A-2B is described; however, it should be understood that one or more additional pairs of vertical field effect transistors (e.g., see pair **262**) could simultaneously be formed. To form a pair of vertical field effect transistors, such as the pair **261** in FIGS. 2A-2B, a mandrel **204** can be formed on the semiconductor layer **203** and sidewall spacers **205** can be formed on opposing sidewalls of the mandrel **204** (**1206-1208**, see FIG. 14). The mandrel **204** can be formed, for example, by depositing a mandrel material layer on the semiconductor layer **203**. The mandrel material layer can comprise, for example, a dielectric material, such as silicon dioxide, or any other suitable mandrel material that can be selectively etched over the semiconductor layer **203** below. The mandrel material layer can then be lithographically patterned and etched to form an essentially rectangular-shaped body (referred to herein as a mandrel) above the semiconductor layer **203**. Next, sidewall spacers **205** can be formed on the opposing sidewalls of the mandrel **204** using conventional sidewall spacer formation techniques. The sidewall spacers **205** can comprise, for example, another dielectric material,

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such as silicon nitride, or any other suitable spacer material that can be selectively etched over the semiconductor layer **203** below. It should be noted that the spacer material should specifically be selected so that the mandrel **204** can also be selectively etched over the sidewall spacers **205**. As a result of processes **1206-1208**, the semiconductor layer **203** will have a masked portion **1401**, which is aligned below the mandrel **204** and the sidewall spacers **205** and which is positioned laterally between unmasked portions **1402**.

Next, the unmasked portions **1402** of the semiconductor layer **203** can be removed (e.g., using an anisotropic reactive ion etch (RIE) process) (**1210**, see FIG. 15). After the unmasked portions **1402** are removed, one or more layers of dielectric material (e.g., silicon dioxide, silicon nitride, etc.) can be deposited so as to laterally surround the masked portion **1401** (**1212**, see FIG. 16). After the dielectric material **271** is deposited, openings **1701** can be formed (e.g., lithographically patterned and etched) such that they extend vertically through the dielectric material **271** and the insulator layer **202** and into the semiconductor substrate **201** below and further such that the masked portion **1401** is positioned laterally between the openings **1701** (**1214**, see FIG. 17). These openings **1701** can then be filled with conductors **248** (also referred to herein as conductive plates) (**1216**, see FIG. 18). The conductive plates **248** can comprise one or more conductive layers comprising, for example, a metal (e.g., copper, tungsten, aluminum or any other suitable metal), a metal alloy, and/or doped polysilicon. The portions of the dielectric material **271** between each conductive plate **248** and the masked portion **1401** of the semiconductor layer **203** will function as a gate dielectric **247** for first and second back gates **245-246** of the first and second vertical field effect transistors **221-222**, respectively, of the pair **261** of vertical field effect transistors.

Then, the mandrel **204** can be selectively removed (**1218**, see FIG. 19). Those skilled in the art will recognize that the etch process used to remove the mandrel **204** will depend upon the materials used for the mandrel **204**, the sidewall spacers **205** and the semiconductor layer **203**. Following removal of the mandrel **204** at process **1218**, an exposed portion **206** of the previously masked portion **1401** of the semiconductor layer **203** between the sidewall spacers **205** can be etched back some distance less than the full thickness of the semiconductor layer **203** (e.g., using an anisotropic RIE process), thereby forming a U-shaped semiconductor body **210** with a first vertical section **212a**, a second vertical section **212b** and a horizontal section **211** between the first vertical section **212a** and the second vertical section **212b** (**1220**, see FIG. 20).

As mentioned above, the wafer provided at process **1202** can comprise a stack of one or more semiconductor layers **203** on an insulator layer **202**. If the wafer comprises only a single semiconductor layer, the U-shaped semiconductor body **210** will similarly comprise only a single semiconductor layer. However, alternatively, the wafer can comprise multiple different semiconductor layers **203** on the insulator layer **202**. In this case, the U-shaped semiconductor body **210** can be formed such the horizontal section **211**, the lower portion of the first and second vertical sections **212a-b** and/or the upper portion of the first and second vertical sections **212a-b** comprise different types of semiconductor materials (e.g., silicon, silicon germanium, silicon germanium carbide, etc.). Those skilled in the art will recognize that different types of semiconductor materials can be used in different components of field effect transistors to tailor strain in the channel region.

After the U-shaped semiconductor body **210** is formed at process **1220**, the sidewall spacers **205** can be selectively

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removed. Those skilled in the art will recognize that the etch process used to remove the sidewall spacers **105** will depend upon the materials used for the sidewall spacers **205**, the dielectric materials **271** and the semiconductor layer **203**. Next, one or more layers of additional dielectric material **272** (e.g., silicon dioxide, silicon nitride, etc.) can be deposited over the semiconductor body **210** and the first and second back gates **245-246**. Following deposition, the additional dielectric material **272** can be planarized to expose the top surfaces of the first and second vertical sections **212a-b** of the semiconductor body **210** (**1222**, see FIG. **21**).

Next, a mask layer **2201** (e.g., a photoresist layer) can be formed with openings that expose the additional dielectric material **272** above the horizontal section **211** of the U-shaped semiconductor body (see FIG. **22**) and the exposed additional dielectric material **272** can be etched back (e.g., using a buffered hydrofluoric acid (BHF) wet etch process) to expose a first inner vertical surface of the first vertical section **212a** and a second inner vertical surface of the second vertical section **212b** (**1224**, see FIG. **23**). It should be noted that this process **1224** should be timed so that etching is stopped before the top surface of the horizontal section **211** is exposed. That is, this etch back process **1224** should be performed such that the horizontal section **211** between the first vertical section **212a** and the second vertical section **212b** remains covered by a relatively thin layer of the additional dielectric material **272**.

After the additional dielectric material **272** is etched back at process **1224**, first and second gates **241-242** can be formed on the thin layer of additional dielectric material **272** above the horizontal section **211** (**1226**, see FIG. **23**). Specifically, a first front gate **241** for the first vertical field effect transistor **221** can be formed adjacent to the exposed first inner vertical surface of the first vertical section **212a** opposite the first back gate **245** and a second front gate **242** for the second vertical field effect transistor **222** can be formed adjacent to the exposed second inner vertical surface of the second vertical section **212b** opposite the second back gate **246**. The first front gate **241** and the second front gate **242** can each be formed so as to comprise, for example, multi-layered spacers. That is, a conformal gate dielectric layer **243** can be deposited such that it is immediately adjacent to the exposed inner vertical surfaces of the first and second vertical sections **212a-b**. The gate dielectric layer **243** can comprise, for example, a silicon dioxide layer, a silicon nitride layer, a silicon oxynitride layer, or any other suitable gate dielectric layer including, but not limited to, a high-K gate dielectric layer such as a hafnium (Hf)-based gate dielectric layer (e.g., hafnium oxide, hafnium silicon oxide, hafnium silicon oxynitride, hafnium aluminum oxide, etc.) or some other suitable high-K dielectric material (e.g., aluminum oxide, tantalum oxide, zirconium oxide, etc.). Next, a gate conductor layer **244** can be deposited on the gate dielectric layer **243**. The gate conductor layer **244** can comprise, for example, a polysilicon gate conductor layer, a metal gate conductor layer or any other suitable gate conductor layer.

It should be understood that, although a single gate dielectric layer **243** and a single gate conductor layer **244** are illustrated, the gate dielectric layer **243** can comprise a stack of multiple gate dielectric materials and the gate conductor layer **244** can similarly comprise a stack of different gate conductor materials and these different gate conductor materials may vary depending upon the conductivity type of the field effect transistor. For example, for an N-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having an N-type work function that is

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between about 3.9 eV and about 4.2 eV (i.e., an N-type metal gate conductor). Exemplary N-type metal gate conductors can comprise hafnium, zirconium, titanium, tantalum, aluminum, and alloys thereof, such as, hafnium carbide, zirconium carbide, titanium carbide, tantalum carbide, and aluminum carbide. For a P-type field effect transistor, the metal gate conductor layer can comprise a stack of metal and/or metal alloys including, but not limited to, at least one metal gate conductor having a P-type work function that is between about 4.9 eV and about 5.2 eV (i.e., a P-type metal gate conductor). Exemplary P-type metal gate conductors include, for example, ruthenium, palladium, platinum, cobalt, and nickel, as well as metal oxides (aluminum carbon oxide, aluminum titanium carbon oxide, etc.) and metal nitrides (e.g., titanium nitride, titanium silicon nitride, tantalum silicon nitride, titanium aluminum nitride, tantalum aluminum nitride, etc.).

Then, an anisotropic spacer etch process can be performed to remove the gate materials from horizontal surfaces of the semiconductor body **210**, thereby creating multi-layered spacers positioned laterally adjacent to the exposed inner vertical surfaces of the first and second vertical sections **212a-b**. It should be noted that this spacer etch process should be performed so that the upper portions of the first and second vertical sections **212a-b** are also exposed.

It should also be noted that when the additional dielectric material **272** is etched back the opposing ends of the vertical sections **212a-b** may also be exposed, thereby allowing the front gates **241-242** to wrap around those opposing ends during the multi-layer spacer formation process. In this case, in the resulting structure the first and second front gates **241-242** will be positioned laterally adjacent to three sides of the vertical sections **212a-b**. Additionally, if the gate conductor layer **244** of the multi-layered spacers formed as a result of the process steps described above is too narrow to receive a contact, then additional gate conductor deposition and lithographic patterning steps may be required to increase the thickness **292** of the gate conductor layer **244** on one or both of the opposing ends of the first and second vertical sections **212a-b** as compared to the thickness **291** of the gate conductor layer **244** on the vertical surfaces of the first and second vertical sections **212a-b** opposite the first and second back gates **245-246** (as shown in FIG. **24B**).

At various times before, during (i.e., in between), and/or after the above-described processes **1202-1226**, various doping processes can be performed so that in the resulting semiconductor structure **200** and, particularly, in the resulting U-shaped semiconductor body **210**, the horizontal section **211** comprises a shared source/drain region **230** for the pair **261** of vertical field effect transistors, the first vertical section **212a** comprises, for the first vertical field effect transistor **221** in the pair **261**, a first channel region **251** adjacent to the shared source/drain region **230** in the horizontal section **211** and a first source/drain region **231** above the first channel region **251** and, the second vertical section **212b** comprises, for the second vertical field effect transistor **222** in the pair **261**, a second channel region **252** adjacent to the shared source/drain region **230** in the horizontal section **211** and a second source/drain region **232** above the second channel region **252** (**1228**, see FIG. **25**). Thus, for example, these doping processes **1228** can be performed such that the lower portion of the first and second vertical sections **212a-b** containing the first and second channel regions **251-252**, respectively, can have a first type conductivity (e.g., P-type conductivity), whereas the horizontal section **211** containing the shared source/drain region **230** as well as the upper portions of the first and second vertical sections **212a-b** containing the

first and second source/drain regions **231-232** can have a second type conductivity (e.g., N-type conductivity) that is different from the first type conductivity. Optionally, additional doping processes may be performed so that the horizontal and/or vertical sections of the U-shaped semiconductor body **210** comprise one or more additional doped regions (not shown) including, but are not limited to, source/drain extension regions and/or halo regions between the first and second channel regions **251-252** and the shared source/drain region **130** and/or between the first and second channel regions **251-252** and the first and second source/drain regions **231-232**.

Optionally, an opening can be formed in the thin layer of additional dielectric material **272** on the horizontal section **211** (e.g., using lithographic patterning and etch techniques) and silicide layers **290** can be formed on the exposed top surfaces of the first and second vertical sections **212a-b** and the center portion of the horizontal section **211** (**1230**, see FIGS. **2A-2B**). The silicide layer(s) **290** can be formed using conventional processing techniques. For example, a layer of a refractory or noble metal (e.g., nickel (Ni), cobalt (Co), tungsten (W), chromium (Cr), platinum (Pt), titanium (Ti), molybdenum (Mo), palladium (Pd), etc.) or an alloy thereof can be conformally deposited over the structure and, specifically, onto the exposed semiconductor surfaces. Next, an anneal process can be performed. Any metal remaining present after the anneal process is performed can be selectively removed. It should be noted that this process **1230** of forming the silicide layers **290** can, depending upon the thickness of the horizontal section **211**, consume the entire center portion of the horizontal section **211** such that the shared source/drain region **230** will be divided into two discrete sections separated by a silicide layer **290** (not shown).

After silicide formation, one or more layers of interlayer dielectric material **273** (e.g., silicon dioxide, silicon nitride, borophosphosilicate glass (BPSG), etc.) can be deposited (**1232**). Next, multiple contacts **281-283** can be formed that extend vertically through the interlayer dielectric material **273** to the different components of the pair **261** of vertical field effect transistors (**1234**). Specifically, a shared source/drain region contact **281** can be formed such that it extends vertically through the interlayer dielectric material **273** and further through the thin layer of the additional dielectric material **272** to the center portion of the horizontal section **211** below (i.e., to the shared source/drain region **230**). Thus, this shared source/drain region contact **281** will be positioned laterally between and will be electrically isolated from the first and second front gates **241-242**. Additional source/drain contacts **282** can be formed that extend vertically through the interlayer dielectric material **273** to the first and second source/drain regions **231-232** at the top of the first and second vertical sections **212a-b** of the semiconductor body **210**. Gate contacts **283** can be formed that extend vertically through the interlayer dielectric material **273** to the first and second gates **241-242**. Various techniques for forming either non-self-aligned contacts (as shown) and/or self-aligned contacts can be used at process **1234** to form the contacts **281-283**. Contact formation techniques are well known in the art and, thus, the details are omitted from this specification in order to allow the reader to focus on the salient aspects of the disclosure. Optionally, rather than simply contacting the first and second source/drain regions **231-232**, metal strap(s) **284** (i.e., wire(s), local interconnect(s), etc.) can be formed in the interlayer dielectric material **273** at the top of the first and/or second vertical sections **212a-b** (e.g., using conventional damascene processing techniques) in order to electrically connect the first and/or second source/drain regions **231-232**

of the first and/or second vertical field effect transistors **221-222** in the pair **261** to adjacent pair(s) (e.g., additional pair **162**) of vertical field effect transistors.

It should further be noted that in the semiconductor structures and methods described above, the first type conductivity is referred to as being P-type conductivity and the second type conductivity is referred to as being N-type conductivity. However, alternatively, the reverse can be true. That is, the first type conductivity can comprise N-type conductivity and the second type conductivity can comprise P-type conductivity. Those skilled in the art will recognize that different dopants can be used to achieve the different conductivity types and that the dopants may vary depending upon the different semiconductor materials used. For example, a silicon-based semiconductor material having N-type conductivity is typically doped with an N-type dopant (e.g., a Group V dopant, such as arsenic (As), phosphorous (P) or antimony (Sb)), whereas a silicon-based semiconductor material having P-type conductivity is typically doped with a P-type dopant (e.g., a Group III dopant, such as boron (B) or indium (In)). Alternatively, a gallium nitride (GaN)-based semiconductor material having P-type conductivity is typically doped with magnesium (Mg), whereas a gallium nitride (GaN)-based semiconductor material having a N-type conductivity is typically doped with silicon (Si). Those skilled in the art will also recognize that different conductivity levels will depend upon the relative concentration levels of the dopants.

The terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting of this disclosure. As used herein, the singular forms “a”, “an” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms “includes”, “including”, “comprises” and/or “comprising” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof. The corresponding structures, materials, acts, and equivalents of all means or step plus function elements in the claims below are intended to include any structure, material, or act for performing the function in combination with other claimed elements as specifically claimed. The descriptions of the various embodiments of the present invention have been presented for purposes of illustration, but are not intended to be exhaustive or limited to the embodiments disclosed. Many modifications and variations will be apparent to those of ordinary skill in the art without departing from the scope and spirit of the described embodiments. The terminology used herein was chosen to best explain the principles of the embodiments, the practical application or technical improvement over technologies found in the marketplace, or to enable others of ordinary skill in the art to understand the embodiments disclosed herein.

Therefore, disclosed above are semiconductor structures configured to allow for continued size scaling of field effect transistors and methods of forming the structures. The semiconductor structures each comprise a pair of vertical field effect transistors formed from an essentially U-shaped semiconductor body. This semiconductor body has a horizontal section and first and second vertical sections. The horizontal section can comprise a shared source/drain region for first and second vertical field effect transistors. The first and second vertical sections can each comprise a channel region and a source/drain region above the channel region for the first and second vertical field effect transistors, respectively. In one semiconductor structure, each vertical section has a gate

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wrapped around the channel region. In another semiconductor structure, each vertical section has a front gate positioned adjacent to the inner vertical surface at the channel region and a back gate positioned adjacent to the outer vertical surface at the channel region. In any case, a contact, which is electrically isolated from the gates, can extend vertically to the shared source/drain region in the horizontal section. Optionally, metal strap(s) can electrically connect the pair of vertical field effect transistors to adjacent pair(s) of vertical field effect transistors. In such semiconductor structures, the contact pitch is not limited by gate length as in prior art MUGFET structures since the gate length is in the vertical direction. Thus, the contact pitch can, for example, be less than 50% of the gate length. Additionally, the fin pitch (i.e., the pitch between the vertical sections of the U-shaped semiconductor body) can be larger than the fin pitch in prior art MUGFETs, thereby allowing for good gate fill. Finally, the transistor width is quantized and the thickness of the initial semiconductor layer can be greater than two times the fin height in prior art MUGFETs, thereby improving analog device (e.g., electrostatic discharge device (ESD)) performance.

What is claimed is:

1. A semiconductor structure comprising:

a monocrystalline semiconductor body comprising:

a horizontal section comprising a shared source/drain region for a pair of vertical field effect transistors;

a first vertical section extending vertically from a first end of said horizontal section and comprising, for a first vertical field effect transistor in said pair, a first channel region and a first source/drain region above said first channel region such that said first channel region is stacked vertically between said first end of said horizontal section and said first source/drain region; and,

a second vertical section parallel to said first vertical section and extending vertically from a second end of said horizontal section opposite said first end, said second vertical section comprising, for a second vertical field effect transistor in said pair, a second channel region and a second source/drain region above said second channel region such that said second channel region is stacked vertically between said second end of said horizontal section and said second source/drain region;

a first dielectric layer laterally surrounding said horizontal section;

a second dielectric layer on said horizontal section and extending laterally from said first vertical section to said second vertical section, said first dielectric layer and said second dielectric layer having essentially co-planar top surfaces and said second dielectric layer being thinner than said first dielectric layer;

a first gate wrapping around said first vertical section at said first channel region so that, on first opposing sides of said first vertical section, said first gate is above and immediately adjacent to said co-planar top surfaces of said first dielectric layer and said second dielectric layer;

a second gate wrapping around said second vertical section at said second channel region so that, on second opposing sides of said second vertical section, said second gate is above and immediately adjacent to said co-planar top surfaces of said first dielectric layer and said second dielectric layer;

a third dielectric layer on said second dielectric layer above said horizontal section and extending laterally from said first gate to said second gate; and,

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a shared source/drain region contact extending vertically through said third dielectric layer and further through said second dielectric layer to a center portion of said horizontal section such that said shared source/drain contact is positioned laterally between and electrically isolated from said first gate and said second gate.

2. The semiconductor structure of claim 1, said first gate comprising a first gate conductor layer with a first thickness on said first opposing sides of said first vertical section and with a second thickness that is greater than said first thickness on first opposing ends of said first vertical section, and said second gate comprising a second gate conductor layer with said first thickness on said second opposing sides of said second vertical section and with said second thickness on second opposing ends of said second vertical section.

3. The semiconductor structure of claim 1, said first gate and said second gate each comprising multi-layered spacers, each multi-layered spacer comprising a gate dielectric layer and a gate conductor layer positioned laterally adjacent to said gate dielectric layer.

4. The semiconductor structure of claim 1, further comprising silicide layers on top surfaces of said first vertical section, said second vertical section and said center portion of said horizontal section.

5. The semiconductor structure of claim 1, said horizontal section being above and immediately adjacent to an insulator layer on a semiconductor substrate.

6. The semiconductor structure of claim 1, further comprising an additional pair of vertical field effect transistors positioned laterally adjacent to said pair and a metal strap electrically connecting said pair to said additional pair.

7. A semiconductor structure comprising:

a monocrystalline semiconductor body comprising:

a horizontal section comprising a shared source/drain region for a pair of vertical field effect transistors;

a first vertical section extending vertically from a first end of said horizontal section, having first opposing vertical surfaces, and comprising, for a first vertical field effect transistor in said pair, a first channel region and a first source/drain region above said first channel region such that said first channel region is stacked vertically between said first end of said horizontal section and said first source/drain region; and,

a second vertical section parallel to said first vertical section, extending vertically from a second end of said horizontal section opposite said first end, having second opposing vertical surfaces, and comprising, for a second vertical field effect transistor in said pair, a second channel region and a second source/drain region above said second channel region such that said second channel region is stacked vertically between said second end of said horizontal section and said second source/drain region;

a first dielectric layer laterally surrounding said semiconductor body and having a first top surface;

a second dielectric layer on said horizontal section extending laterally between said first vertical section and said second vertical section, said second dielectric layer being thinner than said first dielectric layer and having a second top surface that is below a level of said first top surface;

first gates adjacent to said first opposing vertical surfaces of said first vertical section at said first channel region, said first gates comprising: a first front gate above and immediately adjacent to said second dielectric layer; and a



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first back gate comprising a first conductor that extends vertically through said first dielectric layer opposite said first front gate;

second gates adjacent to said second opposing vertical surfaces of said second vertical section at said second channel region, said second gates comprising: a second front gate above and immediately adjacent to said second dielectric layer; and a second back gate comprising a second conductor extending vertically through said first dielectric layer opposite said second front gate;

a third dielectric layer on said second dielectric layer above said horizontal section and extending laterally from said first front gate to said second front gate; and

a shared source/drain region contact extending vertically through said third dielectric layer and said second dielectric layer to a center portion of said horizontal section such that said shared source/drain contact is positioned between and electrically isolated from said first front gate and said second front gate.

8. The semiconductor structure of claim 7, said first conductor and said second conductor extending vertically below a level of a bottom surface of said horizontal section.

9. The semiconductor structure of claim 7, said first front gate and said second front gate each comprising a multi-layered spacer comprising a gate dielectric layer and a gate conductor layer positioned laterally adjacent to said gate dielectric layer.

10. The semiconductor structure of claim 7, further comprising silicide layers on top surfaces of said first vertical section, said second vertical section and said center portion of said horizontal section.

11. The semiconductor structure of claim 7, said horizontal section being above and immediately adjacent to an insulator layer on a semiconductor substrate.

12. The semiconductor structure of claim 7, further comprising an additional pair of vertical field effect transistors positioned laterally adjacent to said pair and a metal strap electrically connecting said pair to said additional pair.

13. A semiconductor structure comprising:

- an insulator layer;
- an essentially U-shaped monocrystalline semiconductor body above and immediately adjacent to said insulator layer, said semiconductor body comprising multiple stacked layers of at least two different monocrystalline semiconductor materials and further comprising:
  - a horizontal section on said insulator layer and comprising a shared source/drain region for a pair of vertical field effect transistors;
  - a first vertical section extending vertically from a first end of said horizontal section and comprising, for a first vertical field effect transistor in said pair, a first channel region and a first source/drain region above said first channel region such that said first channel region is stacked vertically between said first end of said horizontal section and said first source/drain region; and,
  - a second vertical section parallel to said first vertical section and extending vertically from a second end of said horizontal section opposite said first end, said second vertical section comprising, for a second vertical field effect transistor in said pair, a second channel region and a second source/drain region above said second channel region such that said second channel region is stacked vertically between said second end of said horizontal section and said second source/drain region;

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- a first dielectric layer on said insulator layer and laterally surrounding said horizontal section;
- a second dielectric layer on said horizontal section and extending laterally from said first vertical section to said second vertical section, said first dielectric layer and said second dielectric layer having essentially co-planar top surfaces and said second dielectric layer being thinner than said first dielectric layer;
- a first gate wrapping around said first vertical section at said first channel region so that, on first opposing sides of said first vertical section, said first gate is above and immediately adjacent to said co-planar top surfaces of said first dielectric layer and said second dielectric layer;
- a second gate wrapping around said second vertical section at said second channel region so that, on second opposing sides of said second vertical section, said second gate is above and immediately adjacent to said co-planar top surfaces of said first dielectric layer and said second dielectric layer;
- a third dielectric layer on said second dielectric layer above said horizontal section and extending laterally from said first gate to said second gate; and,
- a shared source/drain region contact extending vertically through said third dielectric layer and further through said second dielectric layer to a center portion of said horizontal section such that said shared source/drain contact is positioned laterally between and electrically isolated from said first gate and said second gate.

14. The semiconductor structure of claim 13, said first gate comprising a first gate conductor layer with a first thickness on said first opposing sides of said first vertical section and with a second thickness that is greater than said first thickness on first opposing ends of said first vertical section, and said second gate comprising a second gate conductor layer with said first thickness on said second opposing sides of said second vertical section and with said second thickness on second opposing ends of said second vertical section.

15. The semiconductor structure of claim 13, said first gate and said second gate each comprising multi-layered spacers, each multi-layered spacer comprising a gate dielectric layer and a gate conductor layer positioned laterally adjacent to said gate dielectric layer.

16. The semiconductor structure of claim 13, further comprising:

- silicide layers on top surfaces of said first vertical section, said second vertical section and said center portion of said horizontal section; and,
- an additional pair of vertical field effect transistors positioned laterally adjacent to said pair and a metal strap electrically connecting adjacent vertical sections of said pair and said additional pair.

17. A semiconductor structure comprising:

- an insulator layer on a semiconductor substrate;
- an essentially U-shaped monocrystalline semiconductor body above and immediately adjacent to said insulator layer, said semiconductor body comprising multiple stacked layers of at least two different monocrystalline semiconductor materials and further comprising:
  - a horizontal section on said insulator layer and comprising a shared source/drain region for a pair of vertical field effect transistors;
  - a first vertical section extending vertically from a first end of said horizontal section, having first opposing vertical surfaces, and comprising, for a first vertical field effect transistor in said pair, a first channel region and a first source/drain region above said first channel region such that said first channel region is stacked



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vertically between said first end of said horizontal section and said first source/drain region; and,  
 a second vertical section parallel to said first vertical section, extending vertically from a second end of said horizontal section opposite said first end, having second opposing vertical surfaces, and comprising,  
 for a second vertical field effect transistor in said pair,  
 a second channel region and a second source/drain region above said second channel region such that said second channel region is stacked vertically between said second end of said horizontal section and said second source/drain region;  
 a first dielectric layer on said insulator layer and laterally surrounding said semiconductor body, said first dielectric layer having a first top surface;  
 a second dielectric layer on said horizontal section and extending laterally from said first vertical section to said second vertical section, said second dielectric layer being thinner than said first dielectric layer and having a second top surface that is below a level of said first top surface;  
 first gates adjacent to said first opposing vertical surfaces of said first vertical section at said first channel region, said first gates comprising: a first front gate above and immediately adjacent to said second dielectric layer; and a first back gate comprising a first conductor that extends vertically through said first dielectric layer opposite said first front gate;  
 second gates adjacent to said second opposing vertical surfaces of said second vertical section at said second channel region, said second gates comprising: a second

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front gate above and immediately adjacent to said second dielectric layer; and a second back gate comprising a second conductor extending vertically through said first dielectric layer opposite said second front gate;  
 a third dielectric layer on said second dielectric layer above said horizontal section and extending laterally from said first front gate to said second front gate; and  
 a shared source/drain region contact extending vertically through said third dielectric layer and said second dielectric layer to a center portion of said horizontal section such that said shared source/drain contact is positioned between and electrically isolated from said first front gate and said second front gate.  
**18.** The semiconductor structure of claim 17, said first conductor and said second conductor extending vertically through said insulator layer to said semiconductor substrate.  
**19.** The semiconductor structure of claim 17, said first front gate and said second front gate each comprising a multi-layered spacer comprising a gate dielectric layer and a gate conductor layer positioned laterally adjacent to said gate dielectric layer.  
**20.** The semiconductor structure of claim 17, further comprising:  
 silicide layers on top surfaces of said first vertical section, said second vertical section and said center portion of said horizontal section; and  
 an additional pair of vertical field effect transistors positioned laterally adjacent to said pair and a metal strap electrically connecting said pair to said additional pair.

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